



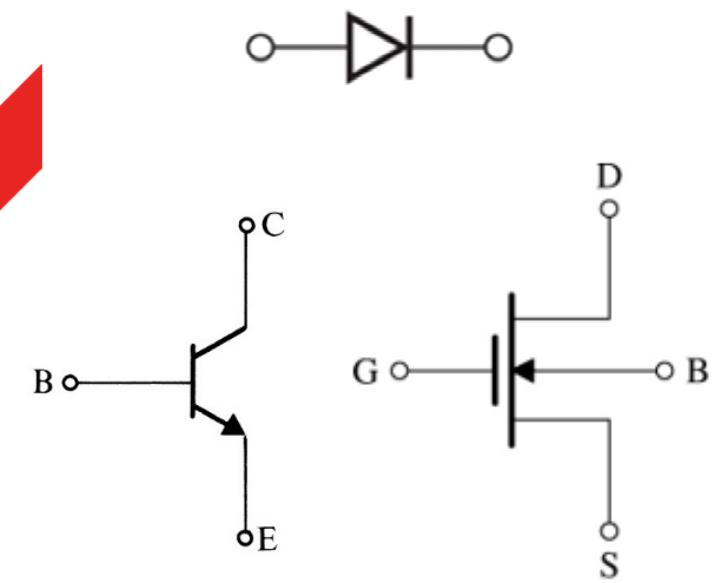
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ELEC2005

Electrical and Electronic Systems

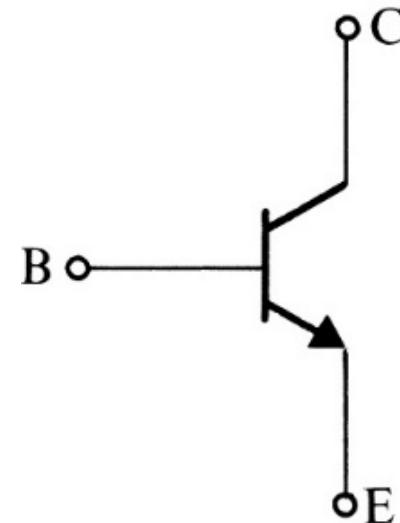
BIPOLAR JUNCTION TRANSISTORS – PART 2

DAVID PAYNE



In Today's Lecture

- Review of BJT characteristics
- Temperature Effects
- BJT Applications
 - ❖ Switches
 - ❖ Amplifiers
 - ❖ Biassing
 - ❖ Small signals





Lecture 4

- 1. Review of BJT Characteristics**
- 2. Temperature Effects**
- 3. BJT Applications**

The Bipolar Junction Transistor



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OVERVIEW

PNP, NPN

Load-line analysis

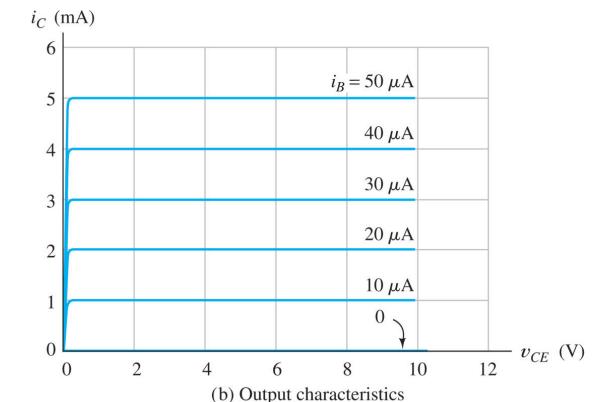
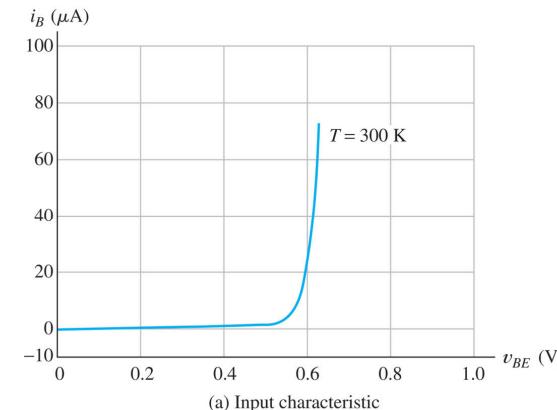
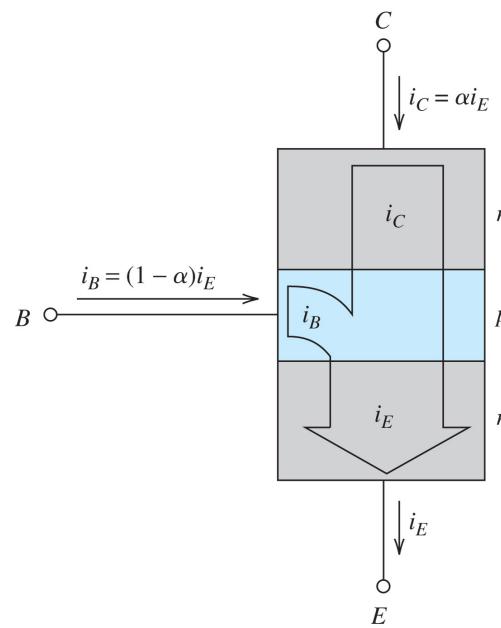
Circuit analysis

Modes of operation

Cut-off

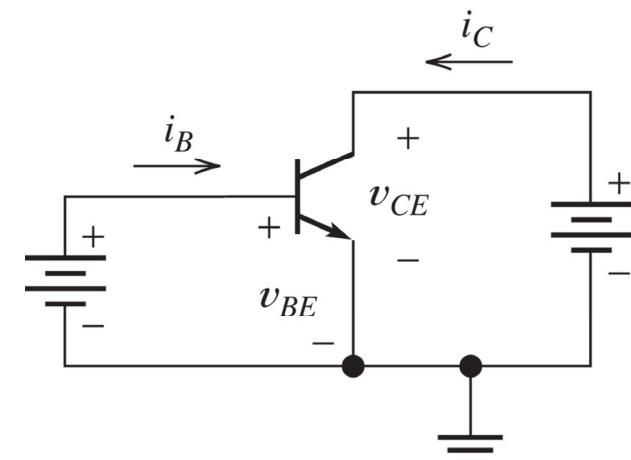
Active

Saturation



BJT Amplifiers

BJT Switches



The Bipolar Junction Transistor



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MODES OF OPERATION

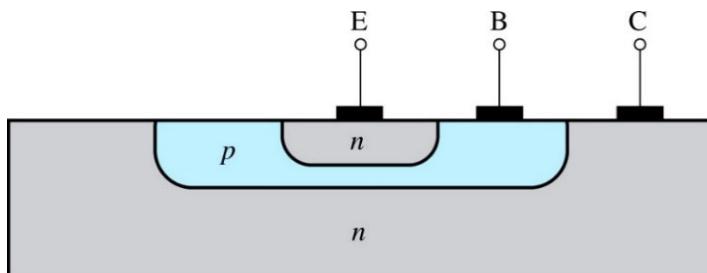
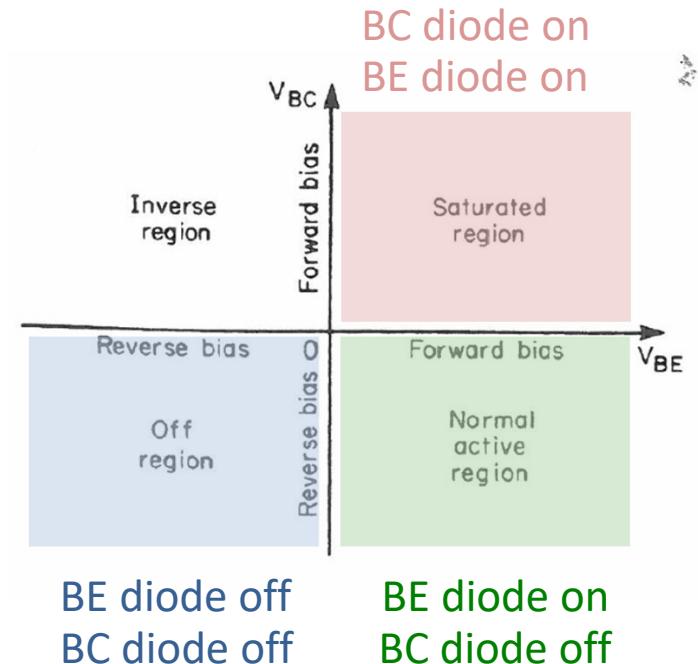
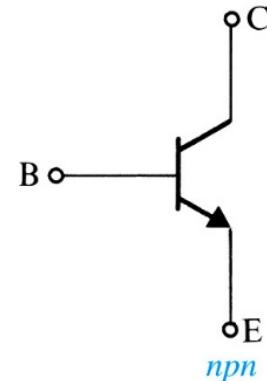


Diagram of physical npn BJT on wafer



Operating mode depends on dc biasing or large signal voltages and currents:

- **active** mode – used for ac amplification
- **cutoff** and **saturation** modes – used for switching.
- BJT is not symmetrical – inverse region is not normally used

The Bipolar Junction Transistor



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ACTIVE REGION

In Active region, BE = Forward biased, BC = Reverse biased

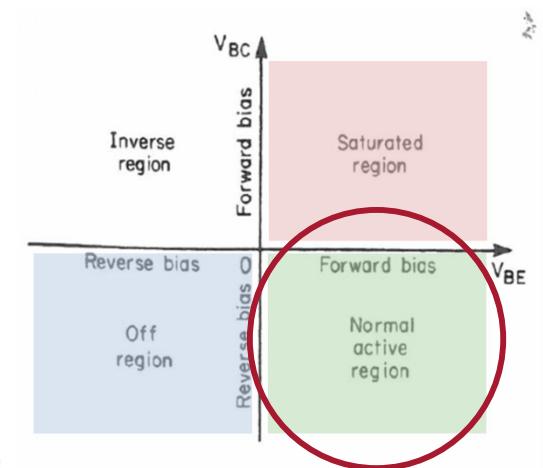
From Kirchoff: $i_E = i_C + i_B$

Base current is much smaller than collector current

We define:

$$i_C = \beta i_B$$

$$i_C = \alpha i_E \quad \alpha = \frac{\beta}{\beta+1}$$



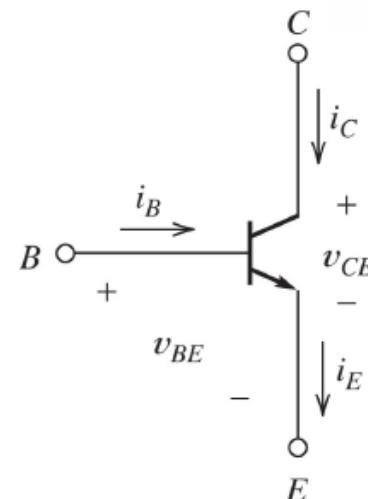
Typical value: $\beta=100$ $\alpha=0.9 - 0.99$

$$i_E = \left(\frac{I_S}{\alpha} \right) \left(e^{v_{BE}/V_T} - 1 \right) \approx \left(\frac{I_S}{\alpha} \right) e^{v_{BE}/V_T}$$

$$i_B \approx \left(\frac{I_S}{\beta} \right) e^{v_{BE}/V_T}$$

$$i_C \approx I_S e^{v_{BE}/V_T}$$

Base-emitter voltage controls the collector current!



Emitter current is the total current.

$$i_E = i_B + i_C = \frac{i_C}{\alpha}$$

The Bipolar Junction Transistor



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LARGE SIGNALS CURRENT SUMMARY

$$V_{CE} > 0 \quad V_A = \infty \quad V_T = \frac{kT}{q} \cong 25 \text{ mV at room temperature}$$

On the formula sheet!

V_{BE}	V_{BC}	$V_{CE} (> 0)$	Mode	$I_C(V_{BE}, V_{CE})$
< 0.5	< 0.4	> 0	cut-off	$I_C \cong 0$
~0.7	> 0.4	< 0.3	saturation	$V_{CE} \cong 0.2 \quad \text{or}$ $I_C = I_S e^{V_{BE}/V_T} - I_{SC} e^{V_{CE}/V_T}$
~0.7	~0.4	~0.3	edge of saturation and active	$I_C = I_S e^{V_{BE}/V_T}$
~0.7	< 0.4	> 0.3	active	$I_C = I_S e^{V_{BE}/V_T}$

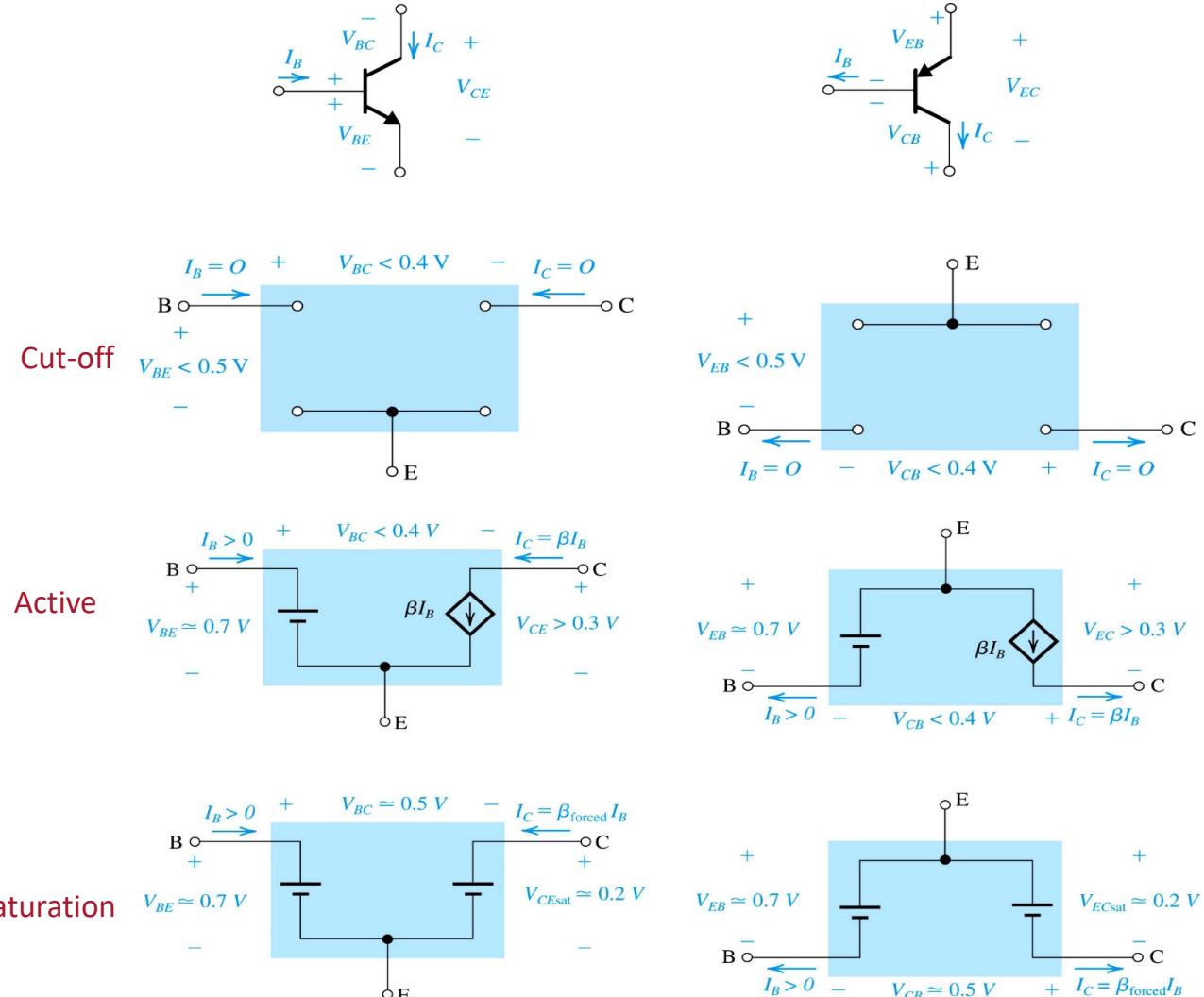
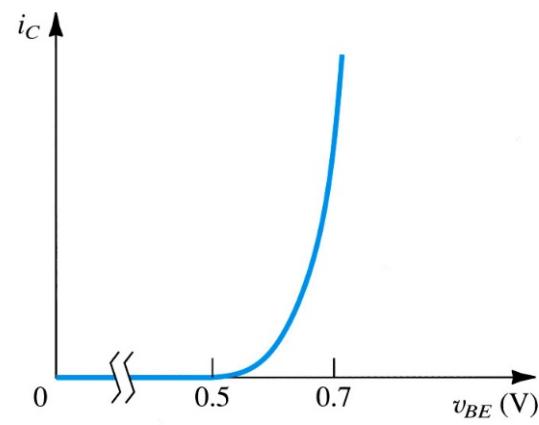
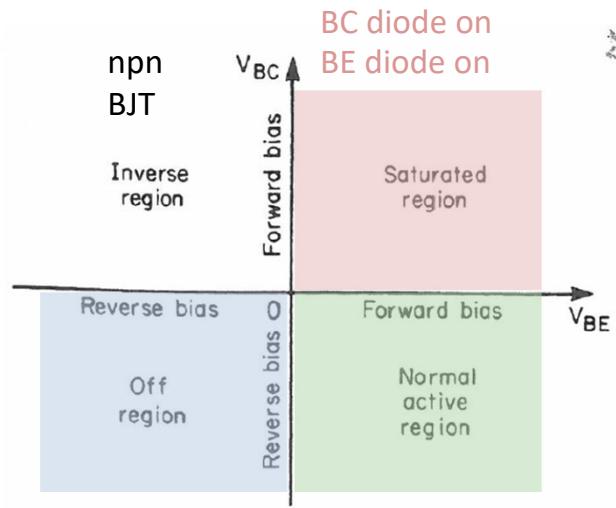
For pnp BJT use the same current equations but with reversed voltage polarities

The Bipolar Junction Transistor



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SUMMARY OF SIMPLE BJT MODELS



Remember these models are only approximate!



Lecture 4

1. Review of BJT Characteristics
2. **Temperature Effects**
3. BJT Applications

The Bipolar Junction Transistor

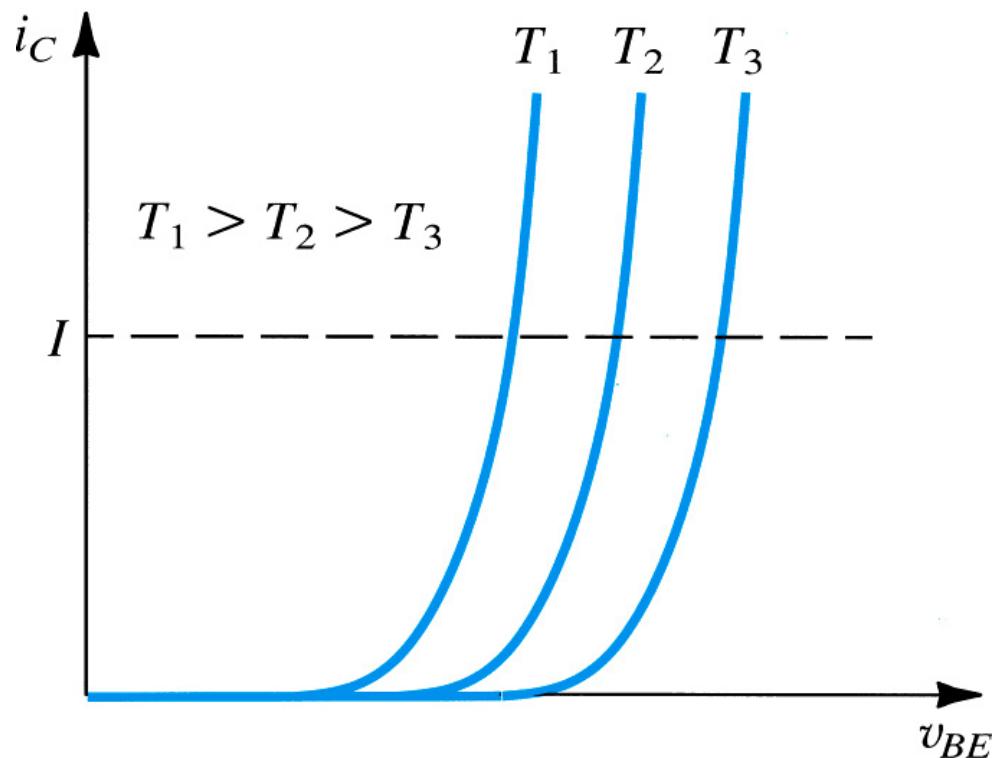


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TEMPERATURE EFFECTS

Temperature has an impact on BJT characteristics

i_C vs v_{BE}



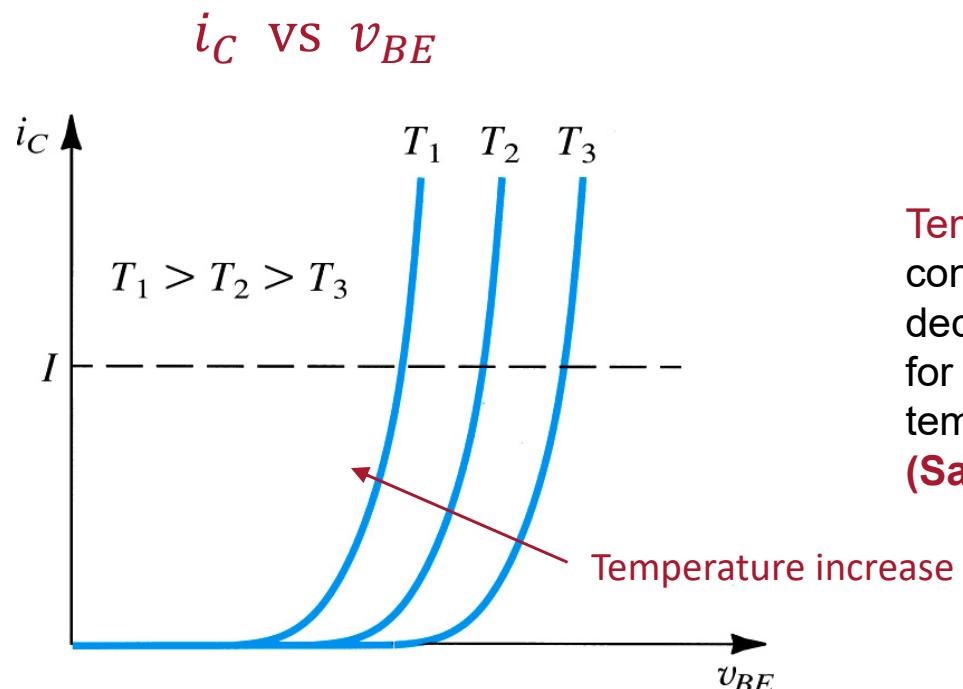
The Bipolar Junction Transistor



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TEMPERATURE EFFECTS

Temperature has an impact on BJT characteristics



Temperature dependence: At a constant current, the voltage decreases by approximately 2 mV for every 1°C increase in temperature.
(Same as the pn junction diode)

Adding a positive voltage source at the B-E junction will cause collector current to keep increasing until burnout!

Add a resistor at the emitter to stop the current increase
(Or use a constant current source)



Lecture 4

1. Review of BJT Characteristics
2. Temperature Effects
3. **BJT Applications**

The Bipolar Junction Transistor

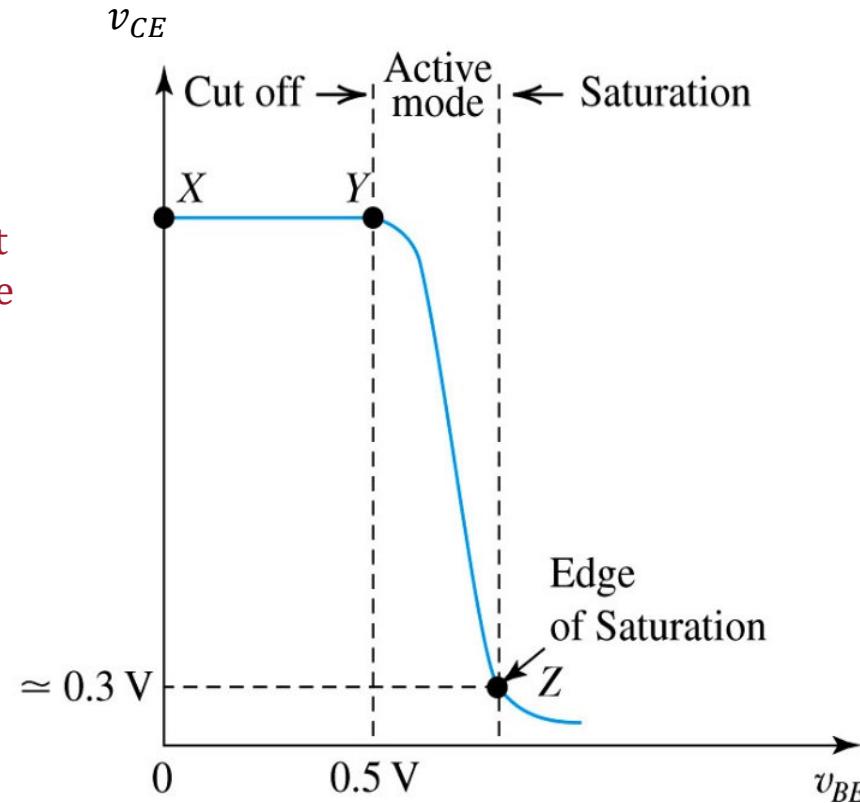
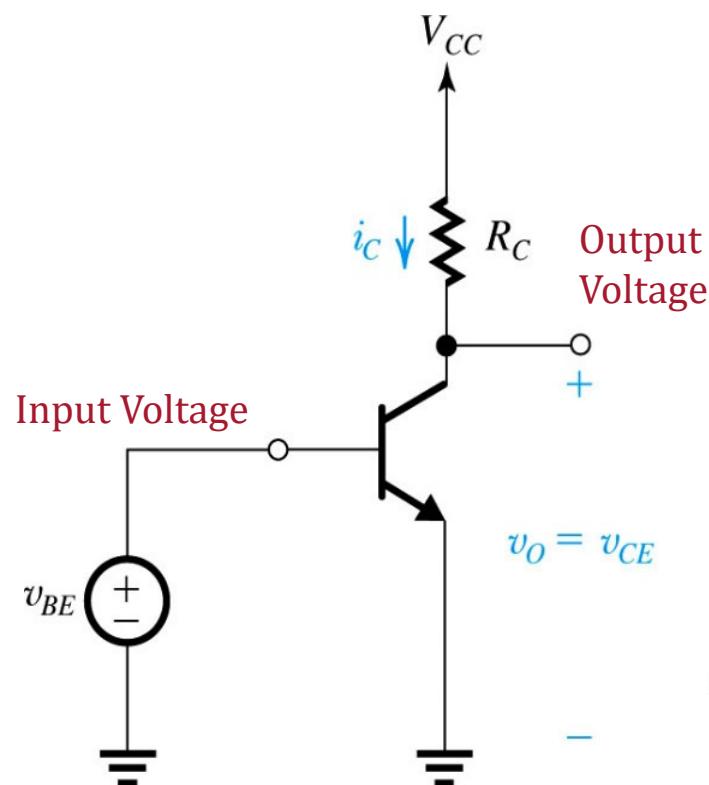


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BJT AS A SWITCH

BJTs can be setup to work as switches or as amplifiers

BJT Switch:



The Bipolar Junction Transistor

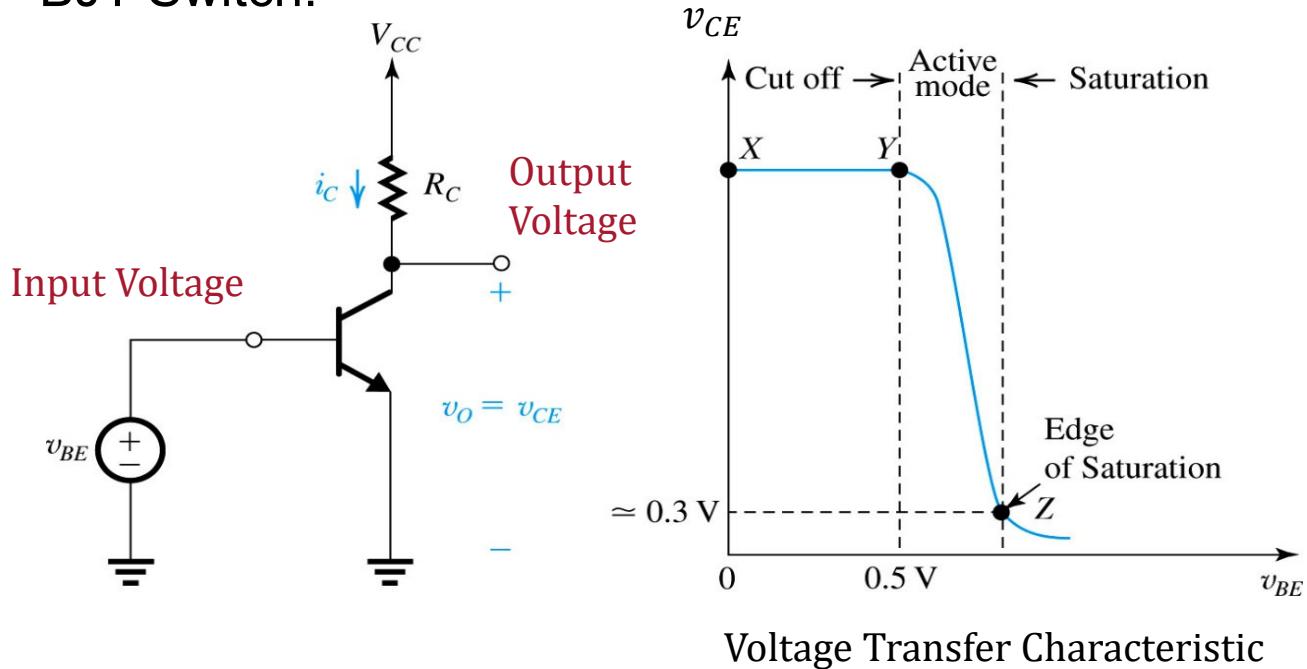


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BJT AS A SWITCH

BJTs can be setup to work as switches or as amplifiers

BJT Switch:



If we increase the input voltage from low to high,
output voltage will switch from high to low.

$$i_C = I_s e^{v_{BE}/V_T}$$

$$v_O = v_{CE} = V_{CC} - R_C i_C$$

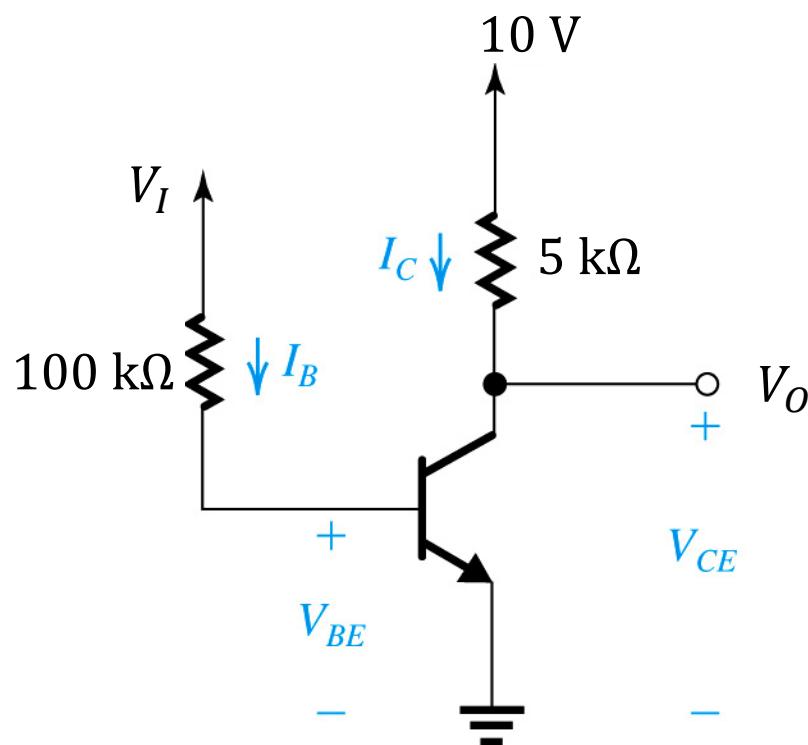
The Bipolar Junction Transistor



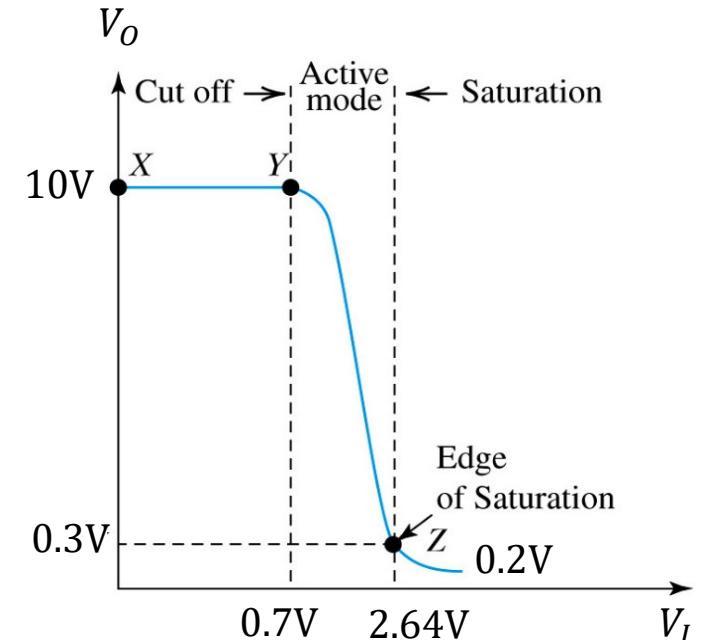
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EXAMPLE

Using the simple BJT model:



$$\beta = 100$$



BJT Applications



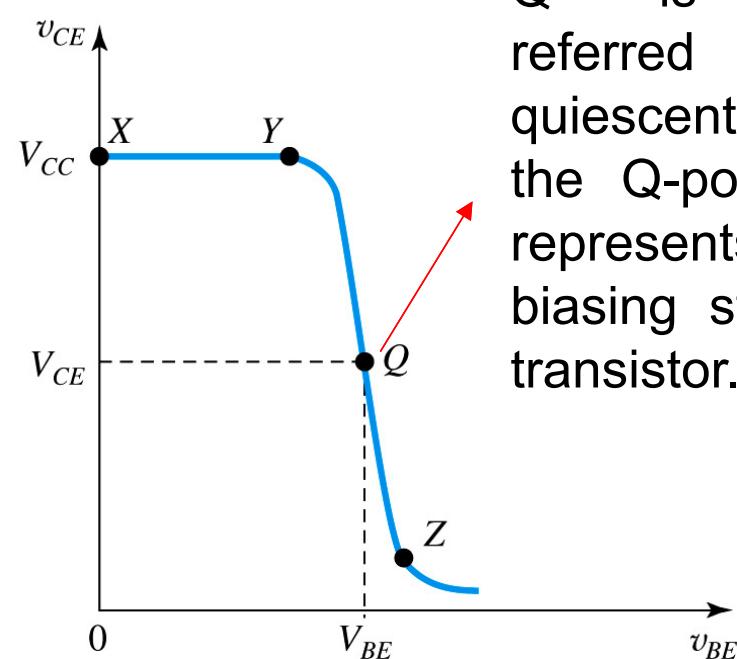
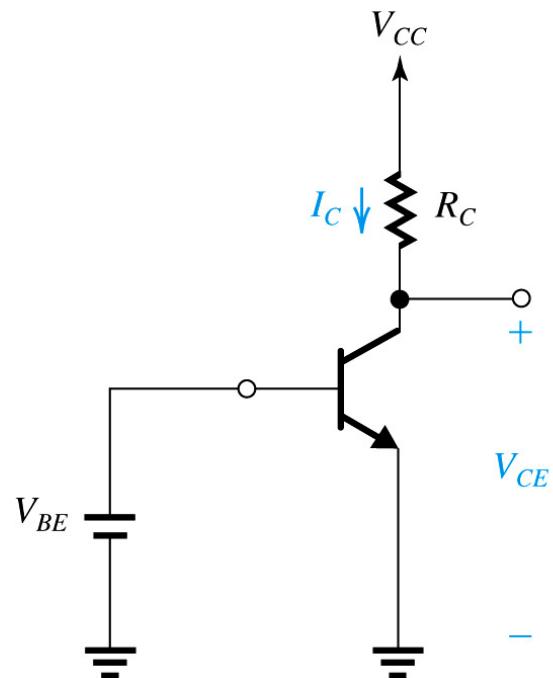
BJT AMPLIFIER

- BJT as an amplifier
- **Biasing** the BJT for linear amplification (small signal)
- The **common emitter** amplifier – load line analysis
- **Small-signal** equivalent circuit
- Examples- Design, Analyse

BJT Amplifier

RECAP – FROM ONLINE CONTENT VIDEOS

We can use V_{BE} to Bias the transistor into active mode (Q)



Q is normally referred to as the quiescent point or the Q-point. And it represents the biasing state of the transistor.

$$I_C = I_S e^{V_{BE}/V_T}$$

$$V_{CE} = V_{CC} - R_C I_S e^{V_{BE}/V_T}$$

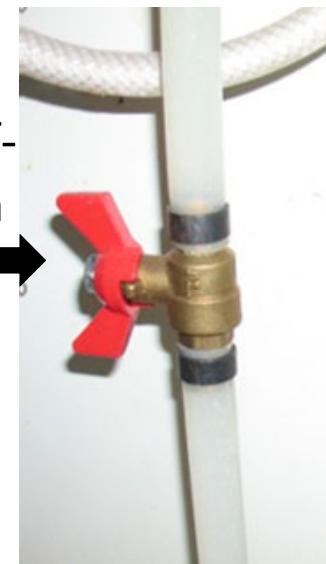
Understanding DC biasing

EXAMPLE

Analogy for an amplifier circuit.

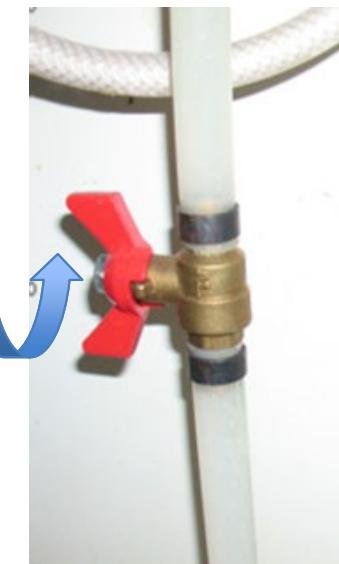


Analogy for DC bias



Water
out

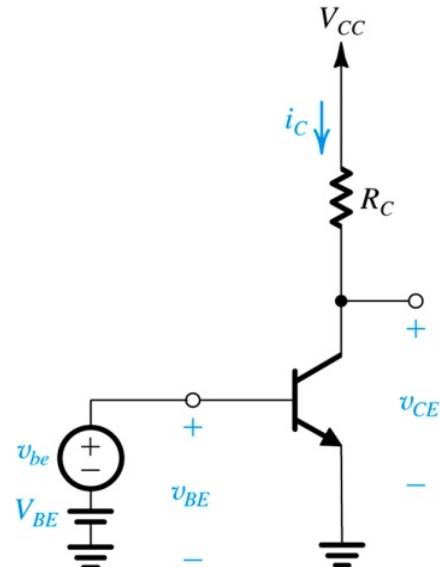
Analogy for DC bias + AC signal



Water
out

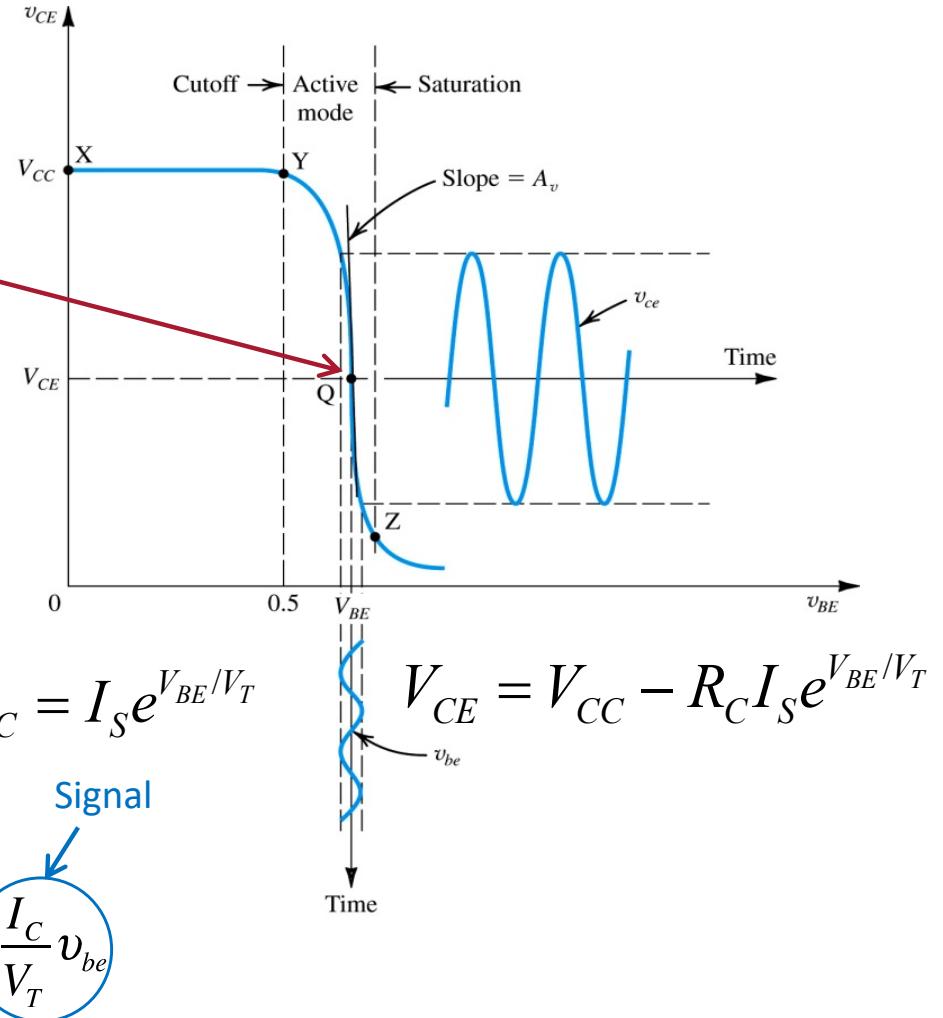
BJT AMPLIFIER

RECAP – FROM ONLINE CONTENT VIDEOS



$$v_{BE}(t) = V_{BE} + v_{be}(t)$$

Dc bias to hold BJT in active mode



if $v_{be} \ll V_T$

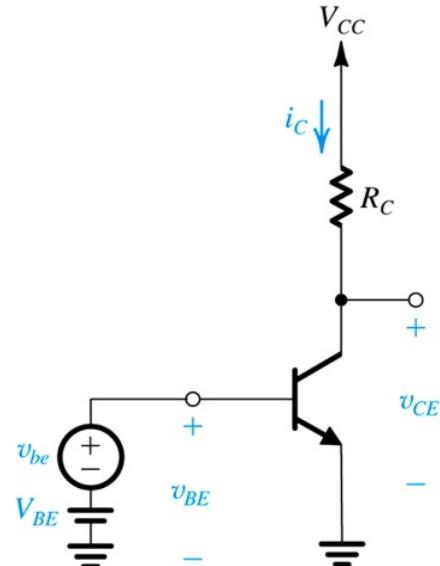
$$i_C = I_S e^{v_{BE}/V_T} = I_S e^{V_{BE}/V_T} e^{v_{be}/V_T} \simeq I_C \left(1 + \frac{v_{be}}{V_T} \right) = I_C + \frac{I_C}{V_T} v_{be}$$

Here we make use of the identity,

$$e^x = 1 + \frac{x}{1!} + \frac{x^2}{2!} + \dots \text{ if } x < 1$$

BJT AMPLIFIER

RECAP – FROM ONLINE CONTENT VIDEOS



$$v_{BE}(t) = V_{BE} + v_{be}(t)$$

if $v_{be} \ll V_T$

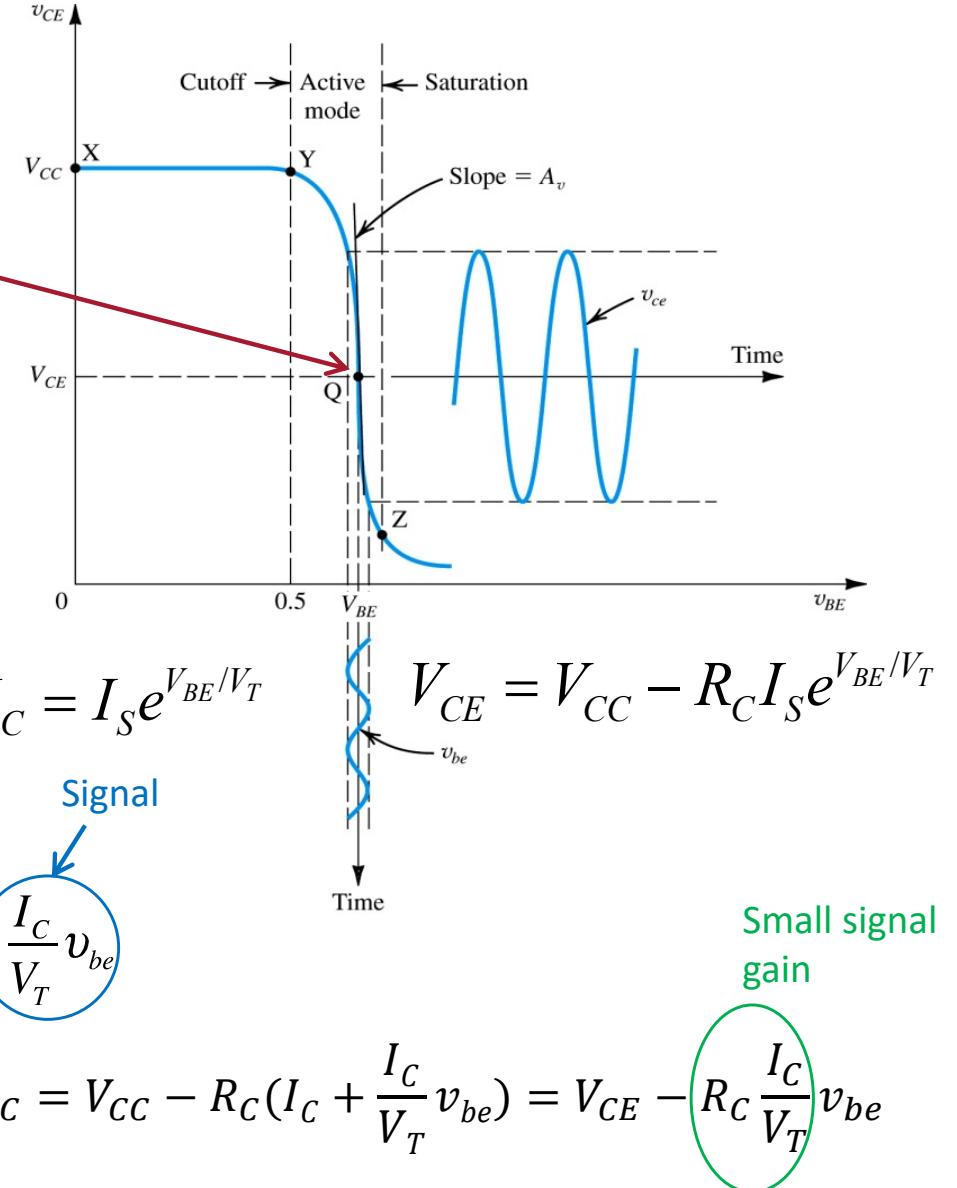
$$i_C = I_S e^{v_{BE}/V_T} = I_S e^{V_{BE}/V_T} e^{v_{be}/V_T} \simeq I_C \left(1 + \frac{v_{be}}{V_T} \right) = I_C + \frac{I_C}{V_T} v_{be}$$

Small signal gain

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$$A_v = \frac{d v_{CE}}{d v_{BE}} \Big|_{v_{BE}=V_{BE}} = -R_C \frac{I_C}{V_T}$$

Dc bias to hold BJT in active mode



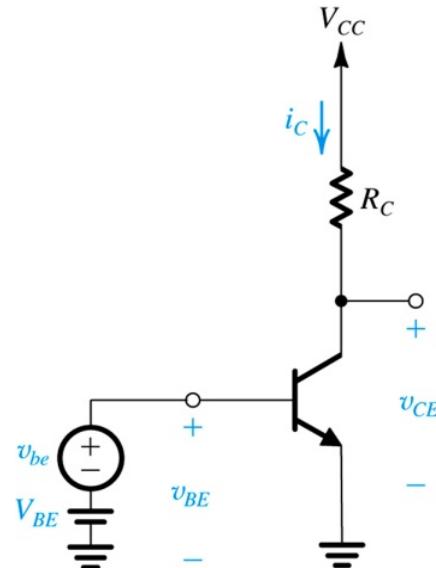
$$v_{CE} = V_{CC} - R_C i_C = V_{CC} - R_C (I_C + \frac{I_C}{V_T} v_{be}) = V_{CE} - R_C \frac{I_C}{V_T} v_{be}$$

BJT AMPLIFIER



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BIASING



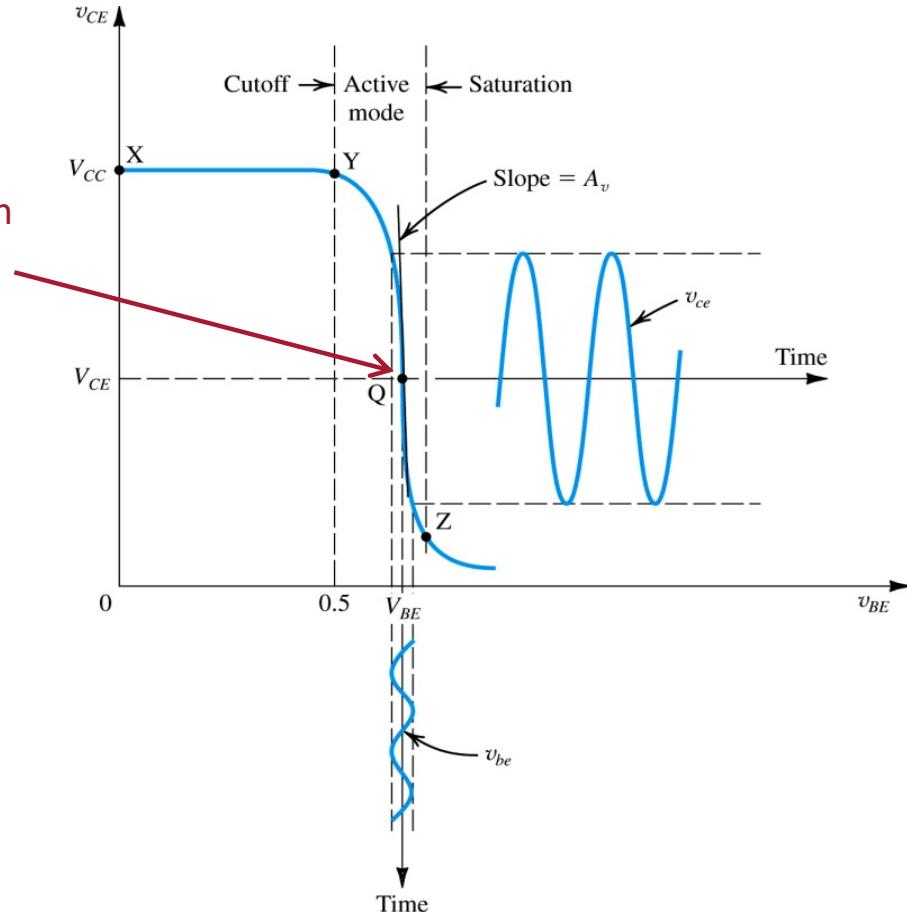
$$v_{BE}(t) = V_{BE} + v_{be}(t)$$

$$v_{be} \ll V_T$$

Small signal voltage gain:

$$A_v = -R_C \frac{I_C}{V_T}$$

Dc bias to hold BJT in active mode



- Gain is negative – inverting amplifier
- Gain depends on bias point
- Only valid for small signal!

BJT Small Signal

TRANSCONDUCTANCE



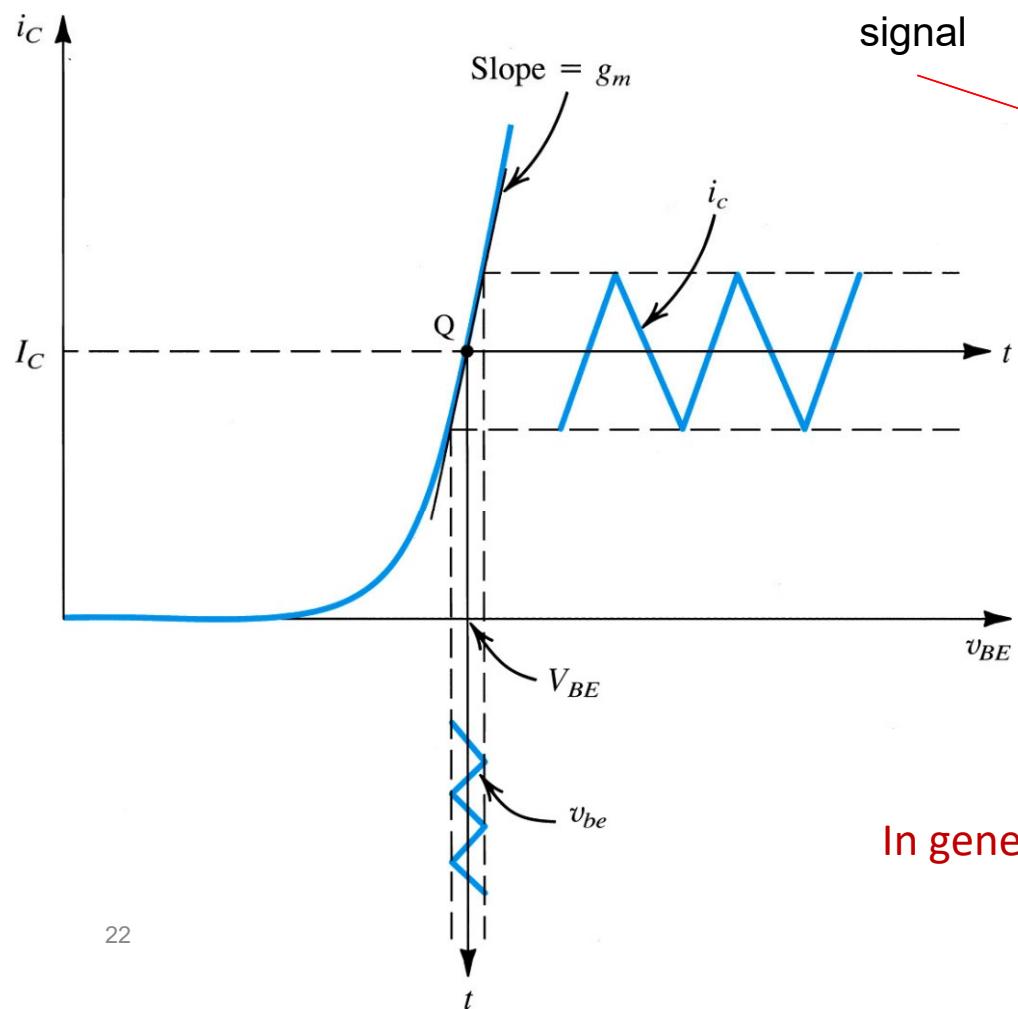
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Total DC signal

$$i_C = I_C + i_c$$

$$i_C = I_S e^{v_{BE}/V_T} = I_S e^{V_{BE}/V_T} e^{v_{be}/V_T} \simeq I_C \left(1 + \frac{v_{be}}{V_T} \right) = I_C + \frac{I_C}{V_T} v_{be}$$

DC signal



$$i_c = \frac{I_C}{V_T} v_{be}$$

$$i_c = g_m v_{be}$$

$$g_m = \frac{I_C}{V_T}$$

In general:

$$g_m = \left[\frac{\partial i_C}{\partial v_{BE}} \right]_{i_C=I_C}$$

Using truncated Taylor's series approximation for small signals (same as the exponential diode)

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MORE ON BIASING

Output current and output voltage

if $v_{be} \ll V_T$

$$i_C =$$

$$I_s e^{v_{BE}/V_T} = I_C e^{v_{be}/V_T} \cong I_C + \frac{I_C}{V_T} v_{be}$$

Total (AC+DC) output current
and voltage

DC

$$= I_C + \frac{I_C}{V_T} v_{be}$$

DC

$$= I_C + g_m v_{be}$$

$$= I_C + g_m v_{be}$$

$$= I_C + R_C \frac{I_C}{V_T} v_{be}$$

$$= V_{CE} - R_C \frac{I_C}{V_T} v_{be}$$

AC

(but depends on
DC operating point!)

BJT AMPLIFIER

MORE ON BIASING



Output current and output voltage after passing through capacitors

$$if v_{be} \ll V_T$$
$$i_c = g_m v_{be}$$
$$v_{ce} = -R_C \frac{I_C}{V_T} v_{be}$$

BJT AMPLIFIER

SETTING THE BIAS POINT

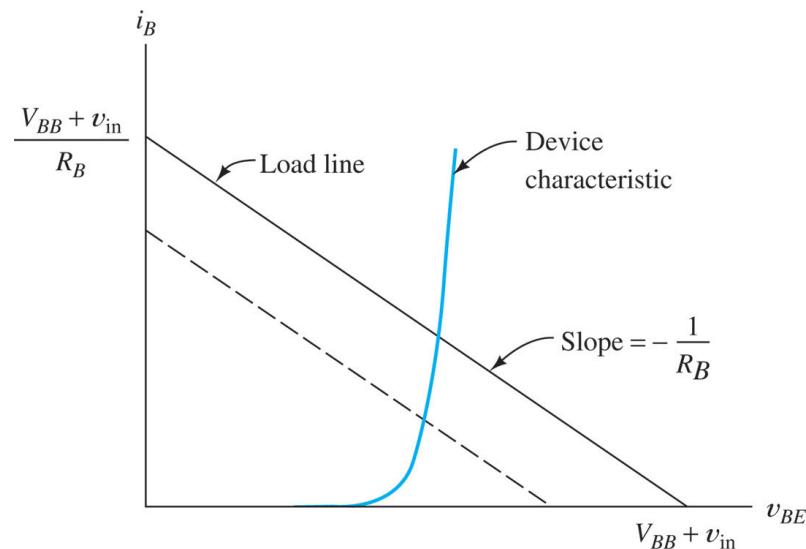
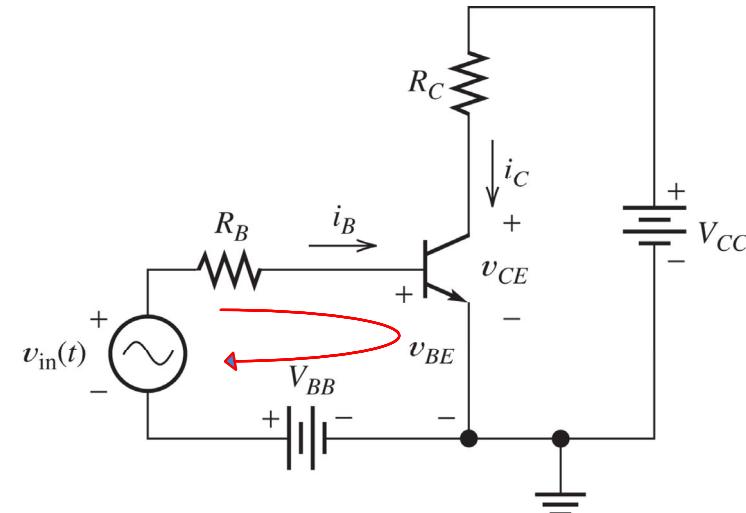


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Input circuit:

$$V_{BB} + v_{in}(t) = R_B i_B(t) + v_{BE}(t)$$

$$i_B(t) = \frac{V_{BB} + v_{in}(t) - v_{BE}(t)}{R_B}$$



(a) Input load line (shifts to dashed line for a smaller value of v_{in})

BJT AMPLIFIER

SETTING THE BIAS POINT

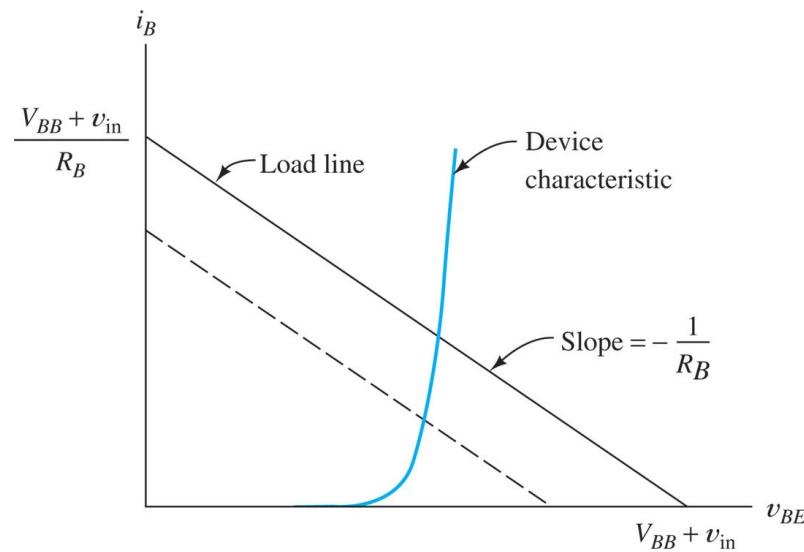


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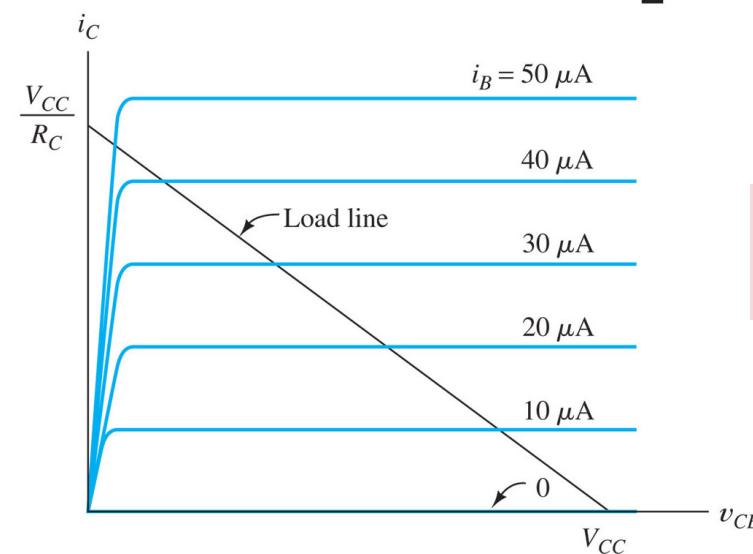
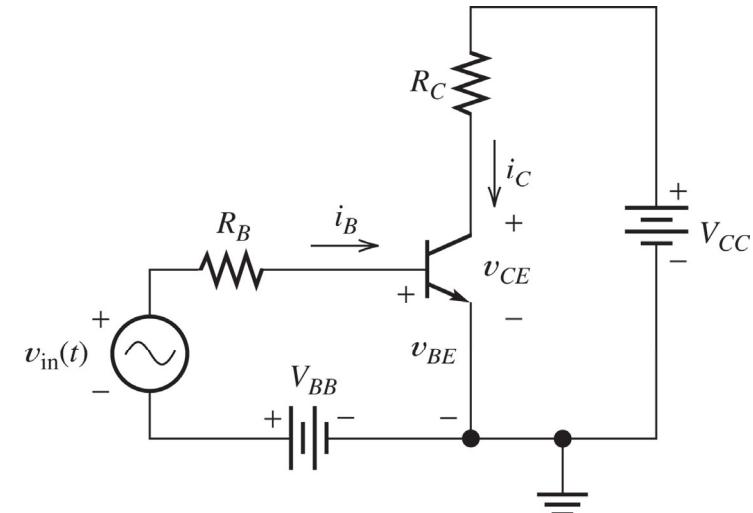
Input circuit:

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$$i_B(t) = \frac{V_{BB} + v_{in}(t) - v_{BE}(t)}{R_B}$$



(a) Input load line (shifts to dashed line for a smaller value of v_{in})



(b) Output

BJT AMPLIFIER



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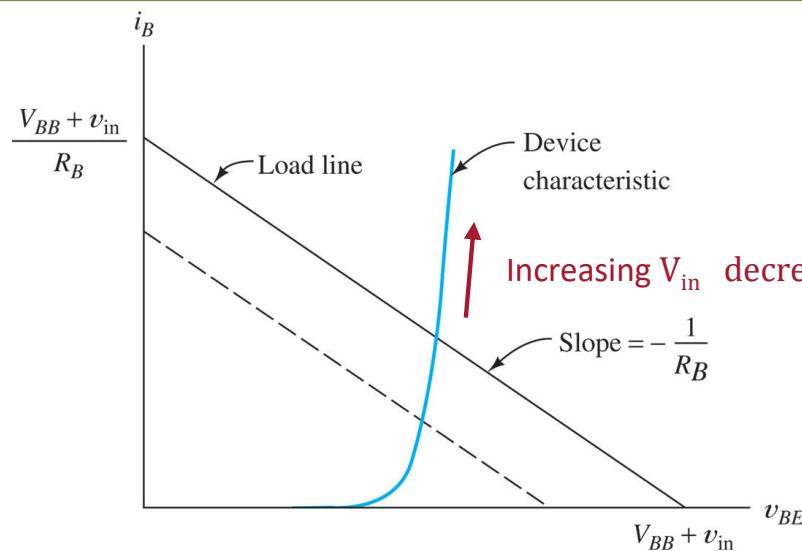
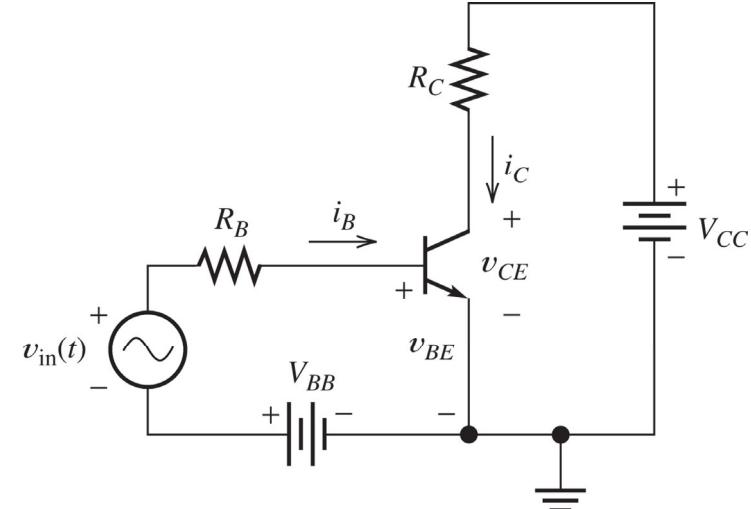
SETTING THE BIAS POINT

Input circuit:

$$V_{BB} + v_{in}(t) = R_B i_B(t) + v_{BE}(t)$$

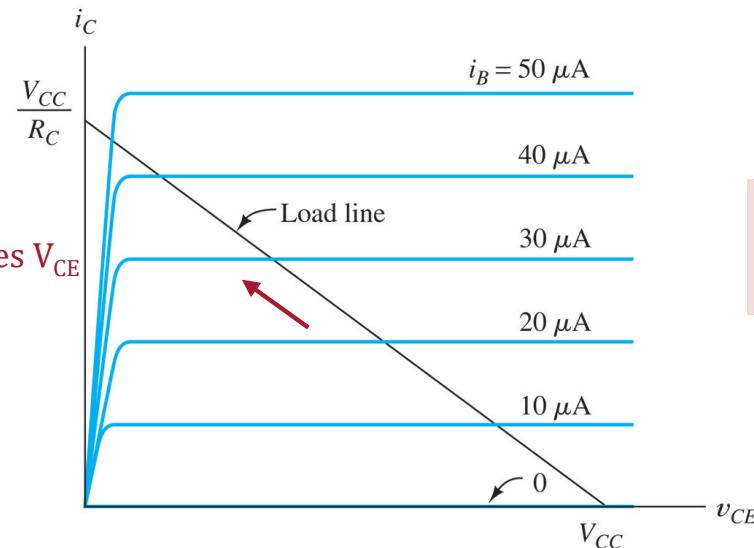
$$i_B(t) = \frac{V_{BB} + v_{in}(t) - v_{BE}(t)}{R_B}$$

We bias the circuit (set the Q point)
assuming 0 small signal voltage



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(a) Input load line (shifts to dashed line for a smaller value of v_{in})

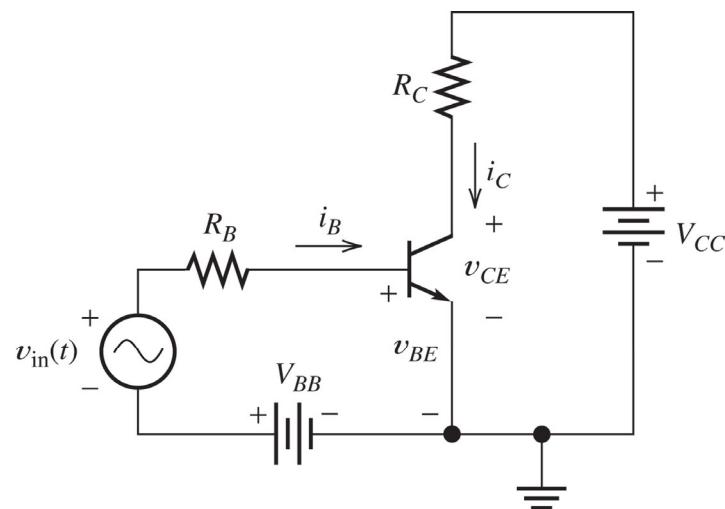


(b) Output

Q point at
 $v_{in} = 0$

BJT AMPLIFIER

LOAD-LINE ANALYSIS EXAMPLE



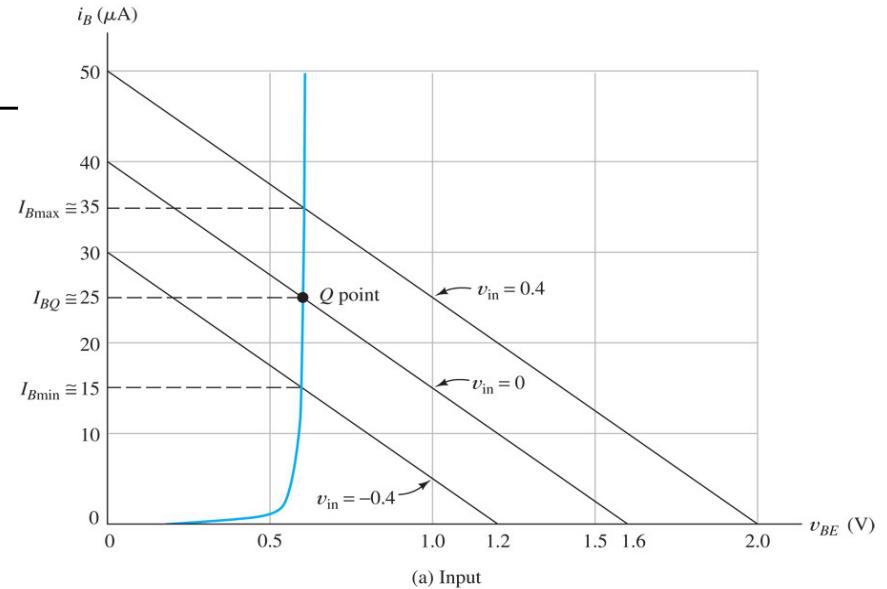
$$V_{CC} = 10 \text{ V}$$

$$V_{BB} = 1.6 \text{ V}$$

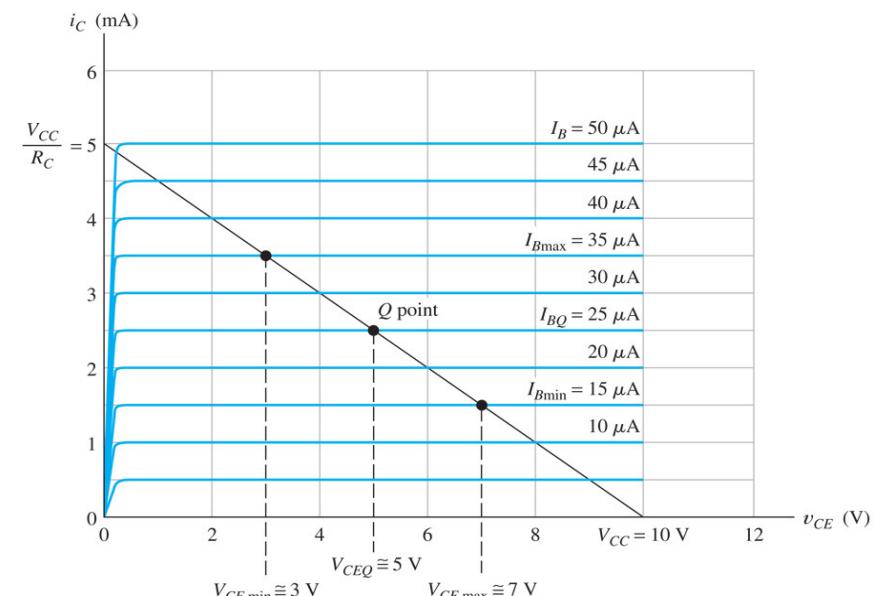
$$R_B = 40 \text{ k}\Omega$$

$$R_C = 2 \text{ k}\Omega$$

$$v_{in}(t) = 0.4 \sin(2000\pi t)$$



(a) Input



(b) Output



What is the voltage gain of this amplifier?

0

PollEv.com/davidpayne187

100 V/V

5 V/V

-100 V/V

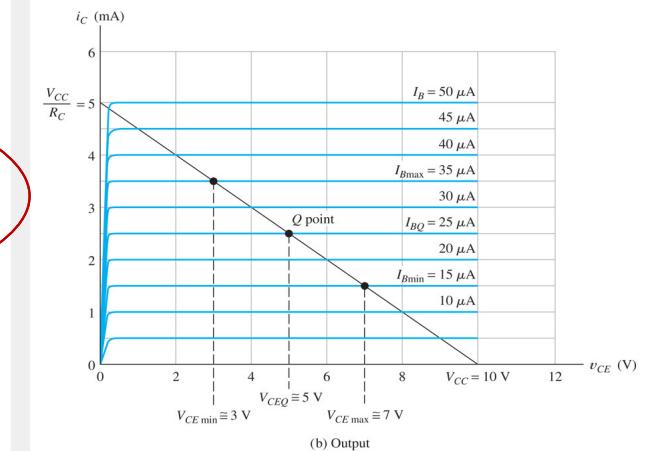
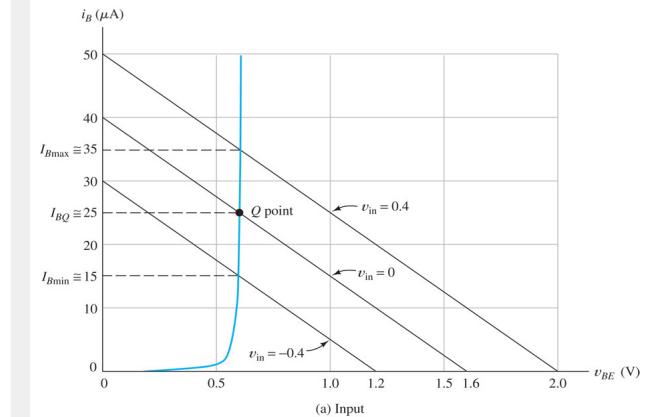
-5V/V

0%

0%

0%

0%



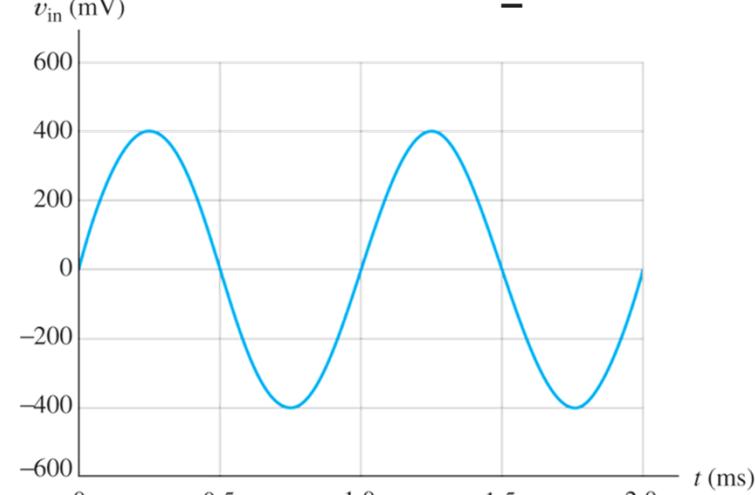
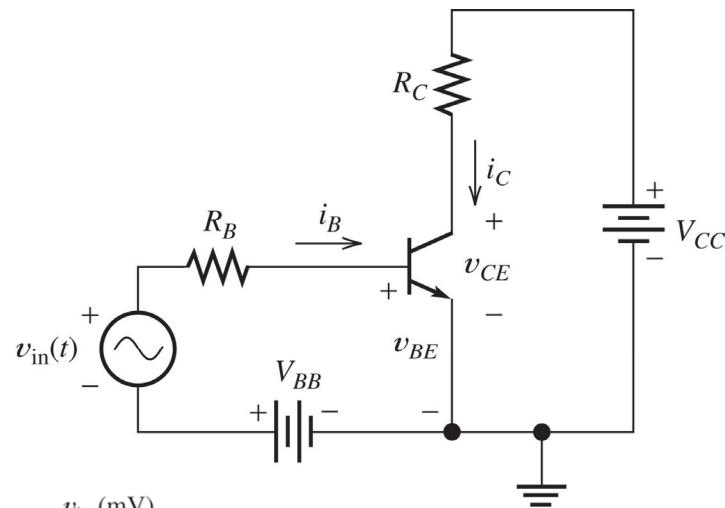
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BJT AMPLIFIER

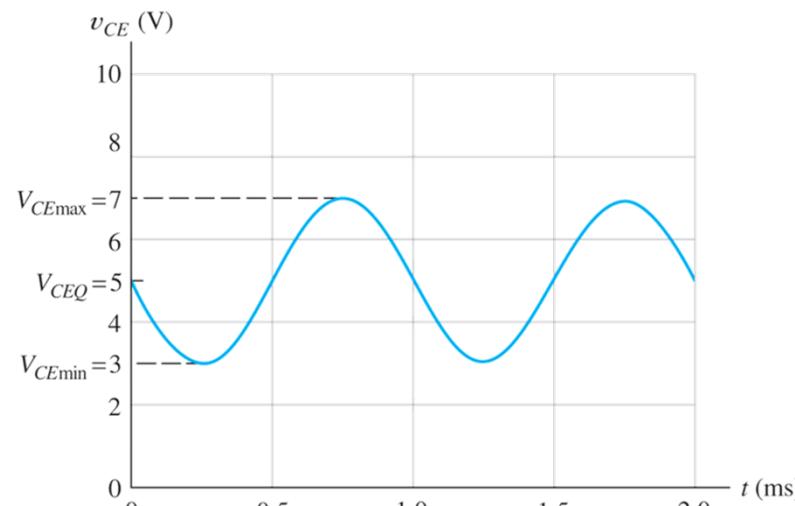
LOAD-LINE ANALYSIS EXAMPLE



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$$\begin{aligned}V_{CC} &= 10 \text{ V} \\V_{BB} &= 1.6 \text{ V} \\R_B &= 40 \text{ k}\Omega \\R_C &= 2 \text{ k}\Omega \\v_{in}(t) &= 0.4 \sin(2000\pi t)\end{aligned}$$



BJT AMPLIFIER

LOAD-LINE ANALYSIS EXAMPLE

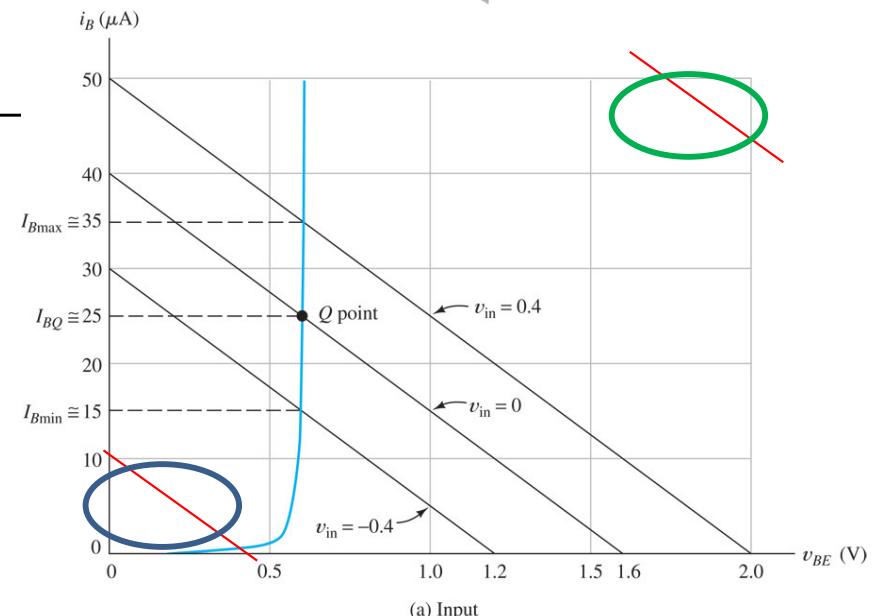
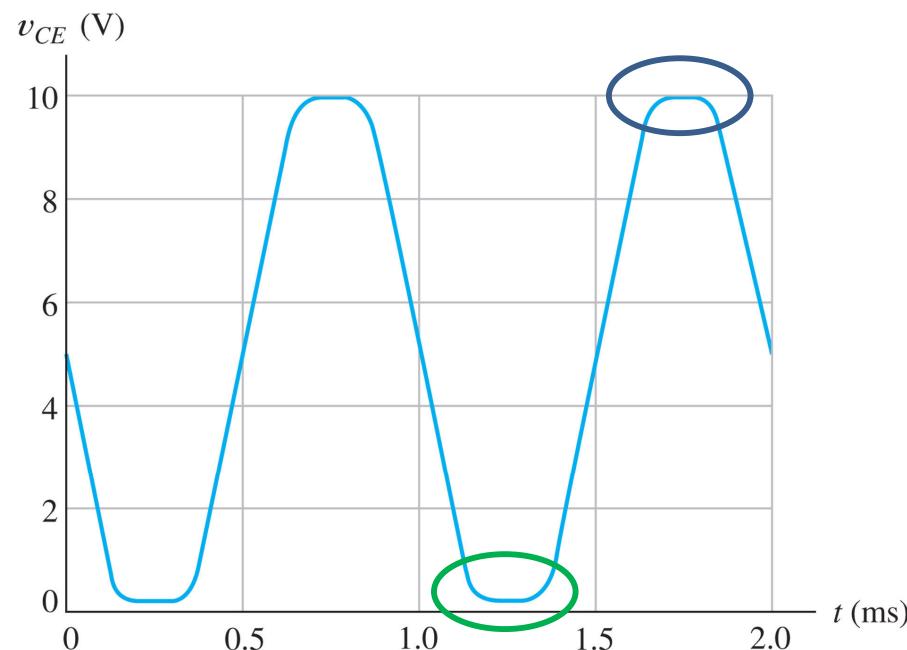
$$V_{CC} = 10 \text{ V}$$

$$V_{BB} = 1.6 \text{ V}$$

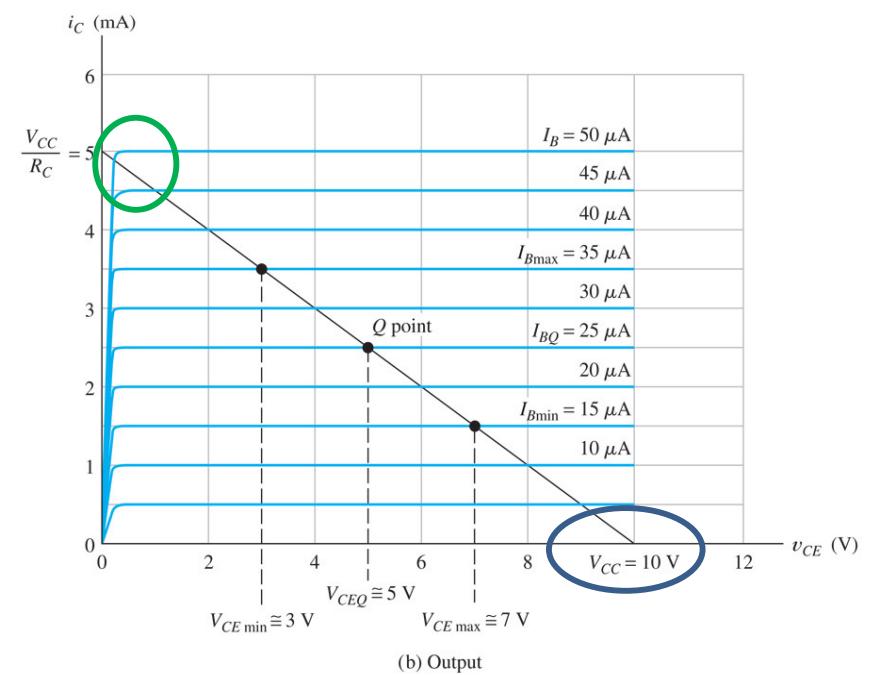
$$R_B = 40 \text{ k}\Omega$$

$$R_C = 2 \text{ k}\Omega$$

$$v_{in}(t) = 1.2 \sin(2000\pi t)$$



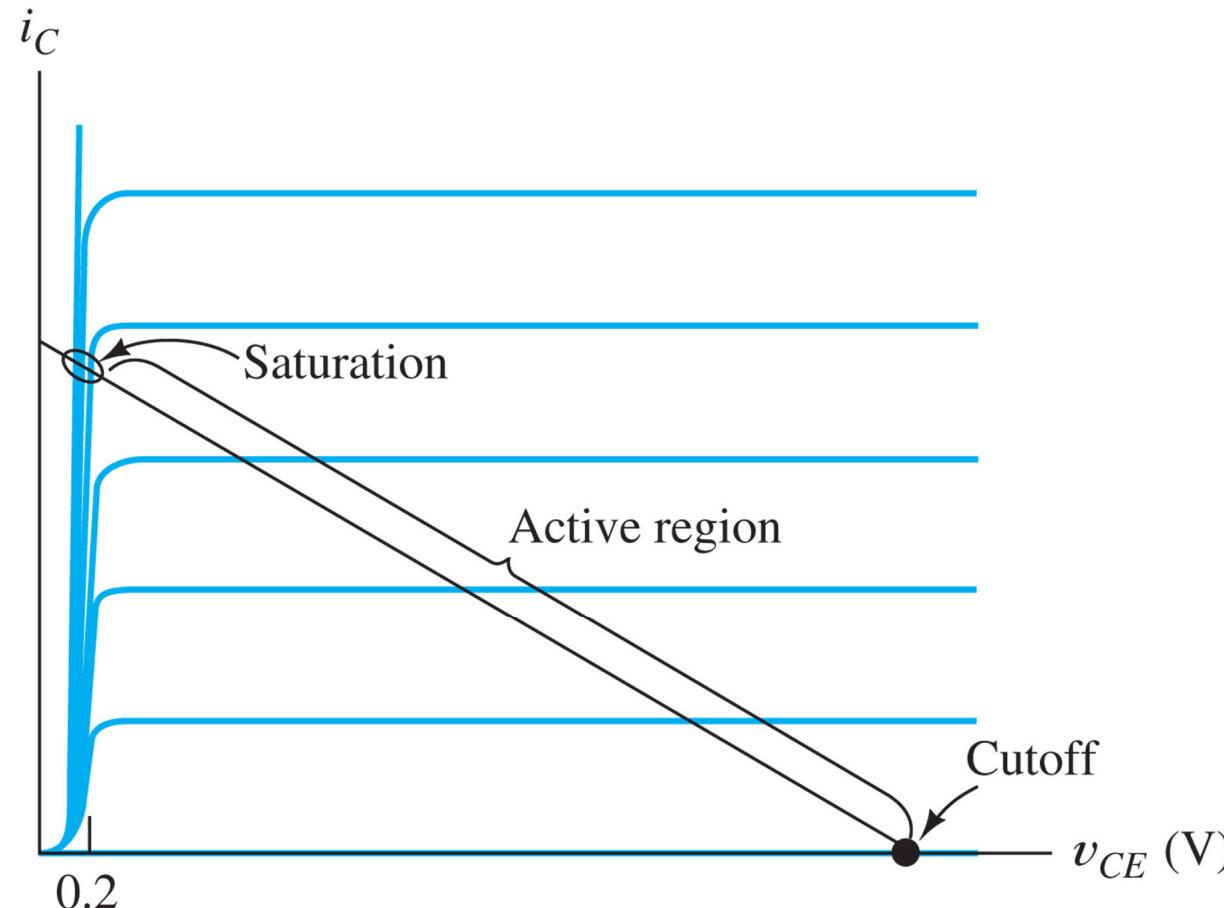
(a) Input



(b) Output

BJT AMPLIFIER

LOAD-LINE ANALYSIS EXAMPLE



Linear amplification only occurs in the active region

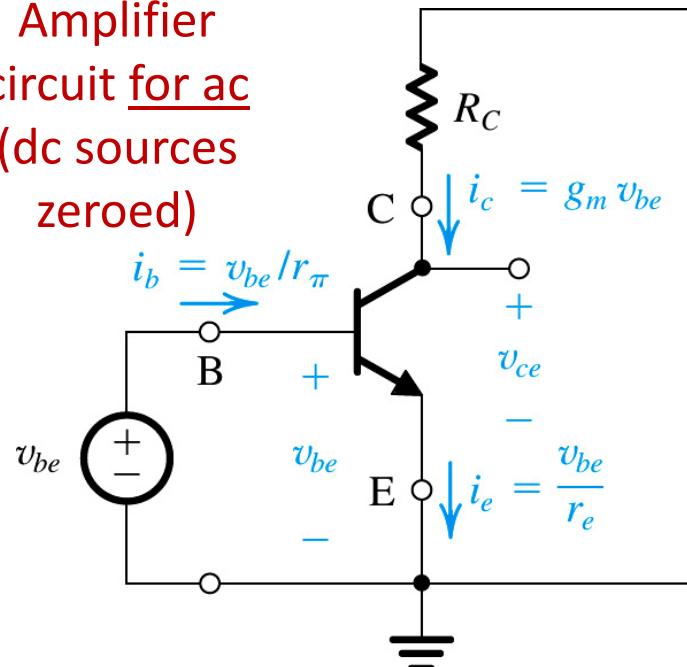
BJT AMPLIFIER

SMALL-SIGNAL AC



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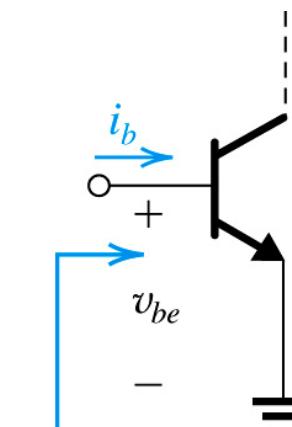
Amplifier
circuit for ac
(dc sources
zeroed)



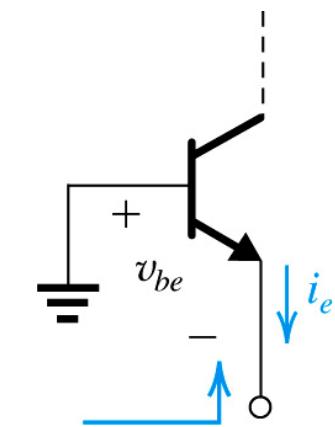
The amplifier circuit with the dc sources (V_{BE} and V_{CC}) eliminated (short-circuited). Thus only the signal components are present. Note that this is a representation of the signal operation of the BJT and not an actual amplifier circuit.

Small-signal gain
of the amplifier

$$v_{ce} = -R_C g_m v_{be} = A_v v_{be}$$



$$r_\pi \equiv \frac{v_{be}}{i_b}$$



$$r_e \equiv \frac{v_{be}}{i_e}$$

BJT small-signal
resistance definitions

BJT Small Signal

RESISTANCE r_π

$$i_c = g_m v_{be}$$

Small signal resistance
looking into the base

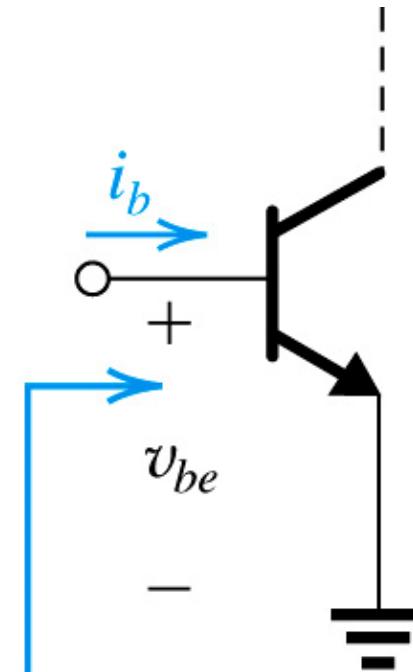
$$i_b = \frac{i_c}{\beta} = \frac{g_m}{\beta} v_{be}$$

$$r_\pi = \frac{v_{be}}{i_b}$$

$$r_\pi = \frac{\beta}{g_m}$$

$$g_m = \frac{I_C}{V_T}$$

$$r_\pi = \frac{V_T}{I_B}$$



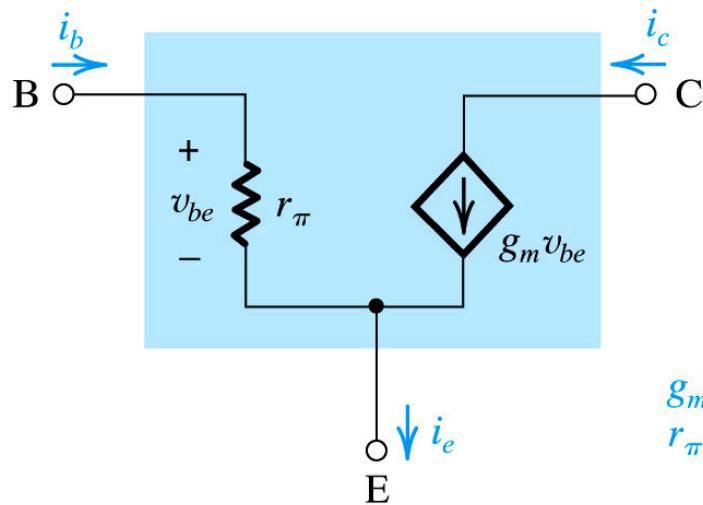
$$r_\pi \equiv \frac{v_{be}}{i_b}$$

BJT Small Signal

MODELS



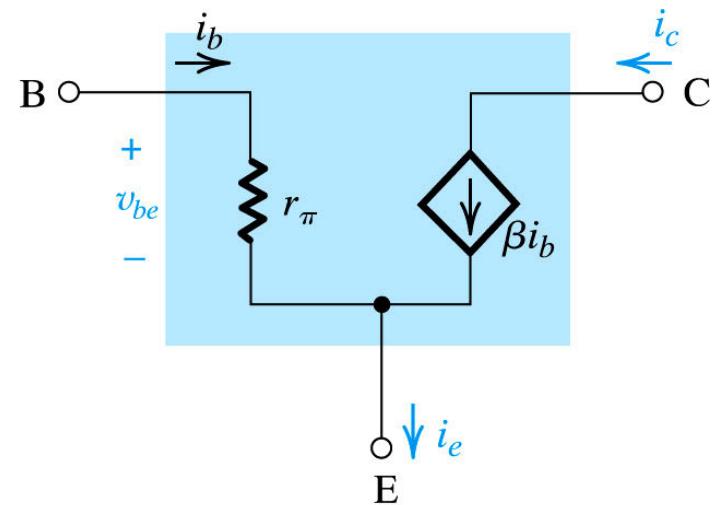
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(a)

$$g_m = I_C / V_T$$

$$r_\pi = \beta / g_m$$



(b)

Two slightly different versions of the hybrid- π model for the small-signal operation of the BJT. The equivalent circuit in (a) represents the BJT as a voltage-controlled current source (a transconductance amplifier), and that in (b) represents the BJT as a current-controlled current source (a current amplifier).

BJT Small Signal

RESISTANCE r_e

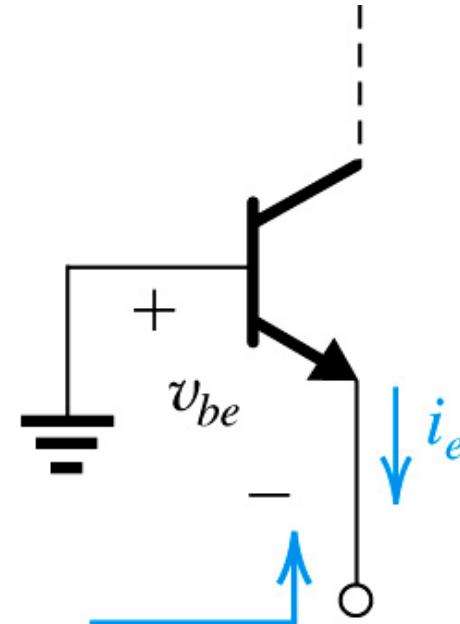
$$i_c = \frac{I_C}{V_T} v_{be}$$

Small signal resistance
looking into the emitter

$$i_e = \frac{i_c}{\alpha} = \frac{I_C}{\alpha V_T} v_{be} = \frac{I_E}{V_T} v_{be}$$

$$r_e = \frac{v_{be}}{i_e}$$

$$r_e = \frac{V_T}{I_E} = \frac{\alpha V_T}{I_C} = \frac{\alpha}{g_m} \simeq \frac{1}{g_m}$$



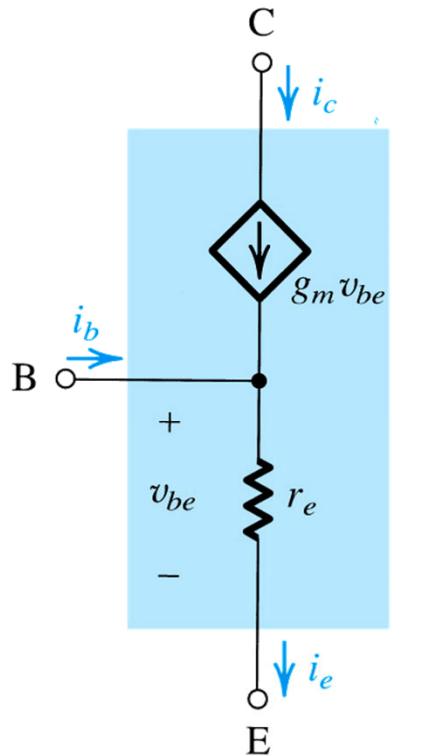
$$r_e \equiv \frac{v_{be}}{i_e}$$

BJT Small Signal

MODELS



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$$g_m = I_C/V_T$$

$$r_e = \frac{V_T}{I_E} = \frac{\alpha}{g_m}$$

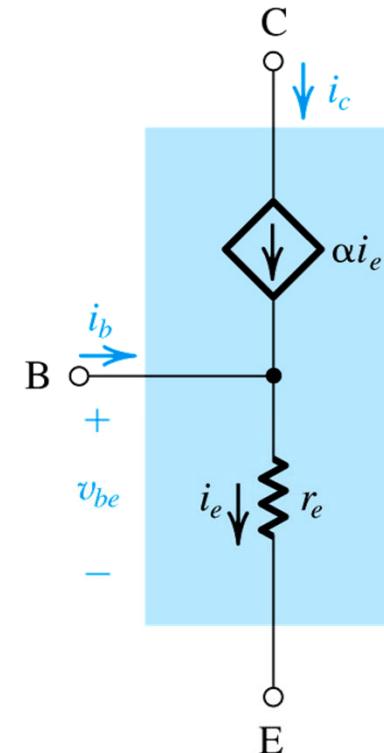


Figure 6.41 Two slightly different versions of what is known as the *T model* of the BJT. The circuit in **(a)** is a voltage-controlled current source representation and that in **(b)** is a current-controlled current source representation. These models explicitly show the emitter resistance r_e rather than the base resistance r_π featured in the hybrid- π model.

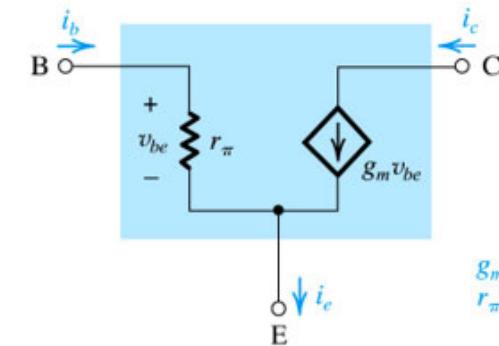
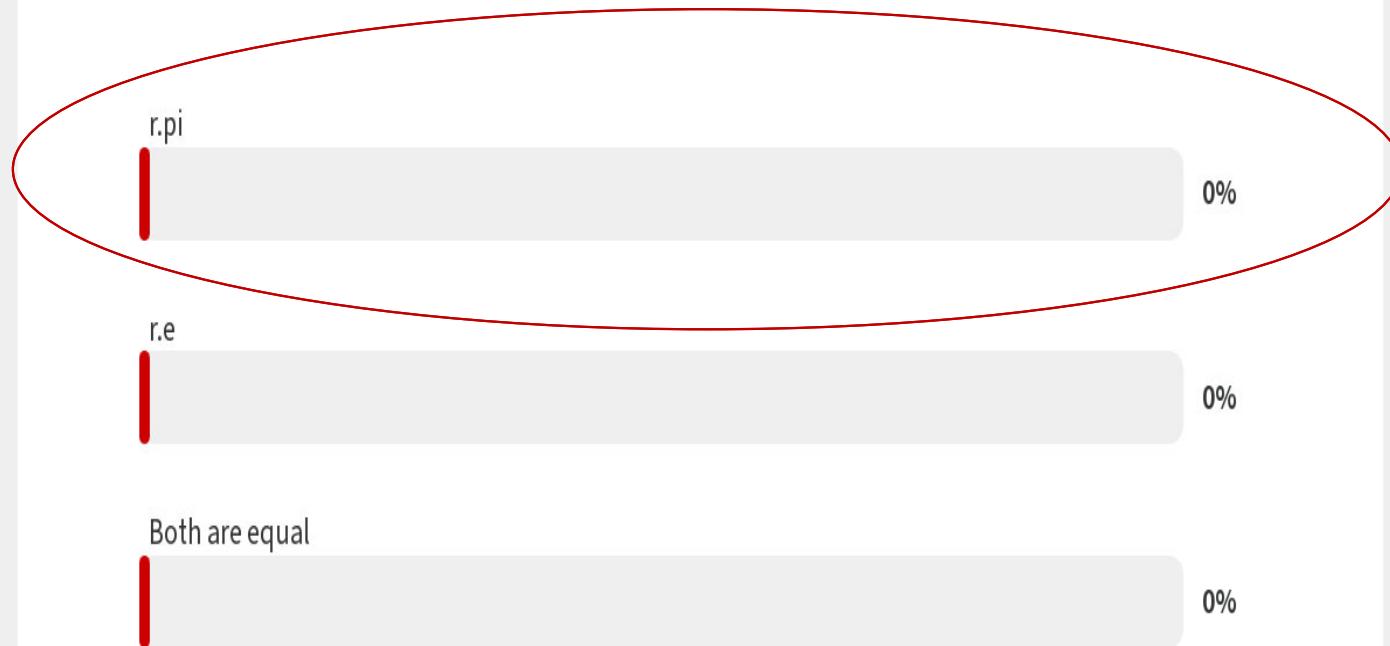
Which is the larger value, r.pi or r.e?

0

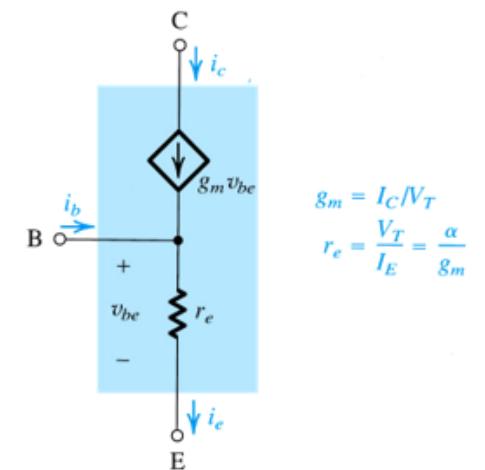


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$$g_m = I_C / V_T$$
$$r_\pi = \beta / g_m$$



$$g_m = I_C / V_T$$
$$r_e = \frac{V_T}{I_E} = \frac{\alpha}{g_m}$$

BJT Small Signal

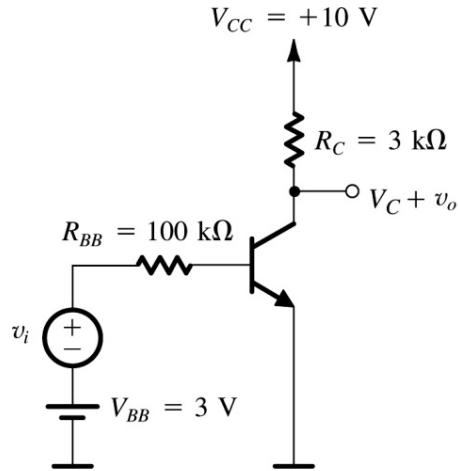


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EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
6.14 for more details



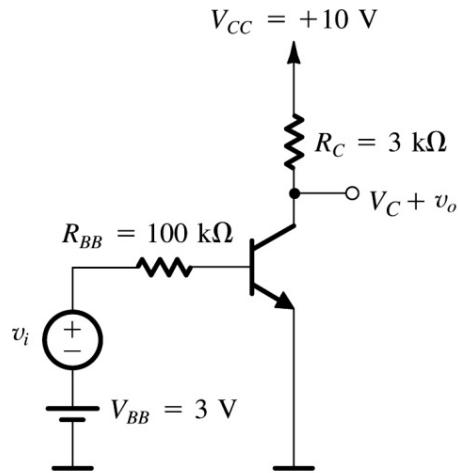
(a)

BJT Small Signal

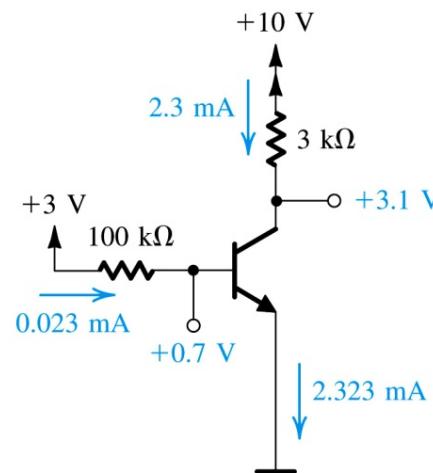
EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
6.14 for more details



(a)



(b)

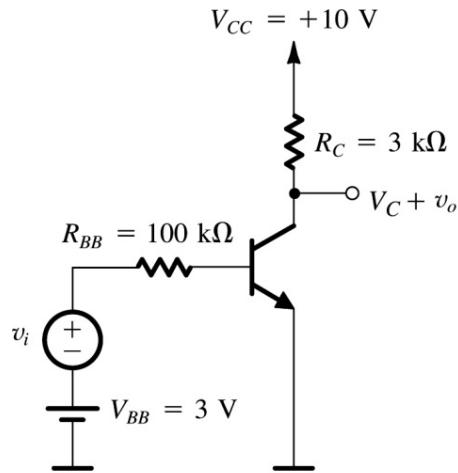
BJT Small Signal

EXAMPLE

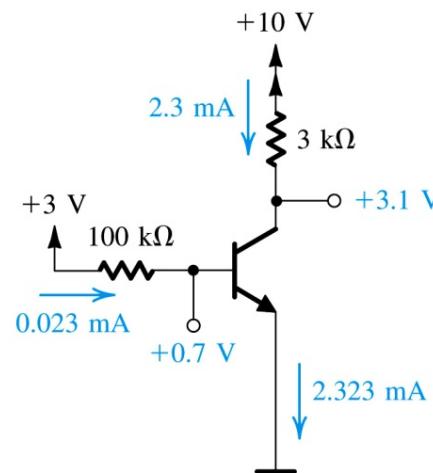


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Find the voltage gain of the following amplifier ($\beta=100$)



(a)



(b)

See Sedra example
6.14 for more details

$$g_m = \frac{I_C}{V_T} = \frac{2.3 \text{ mA}}{25 \text{ mV}} = 92 \text{ mA/V}$$

$$r_\pi = \frac{\beta}{g_m} = \frac{100}{92} \text{ k}\Omega = 1.09 \text{ k}\Omega$$

$$r_e = \frac{V_T}{I_E} = \frac{25 \text{ mV}}{(2.3 / 0.99) \text{ mA}} = 10.8 \Omega$$

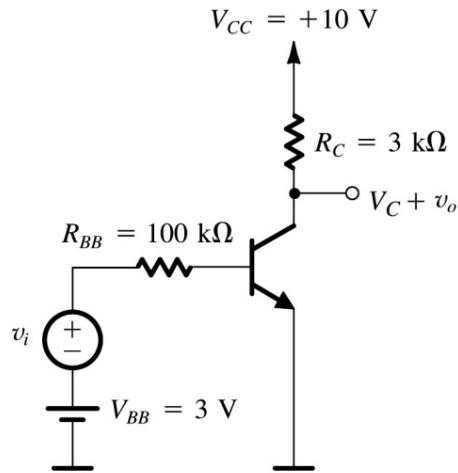
BJT Small Signal



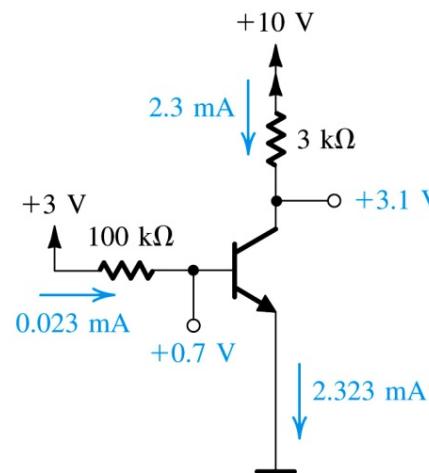
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EXAMPLE

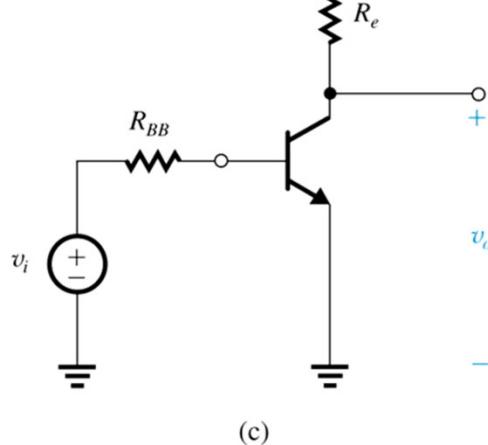
Find the voltage gain of the following amplifier ($\beta=100$)



(a)



(b)



(c)

See Sedra example
6.14 for more details

$$g_m = \frac{I_C}{V_T} = \frac{2.3 \text{ mA}}{25 \text{ mV}} = 92 \text{ mA/V}$$

$$r_\pi = \frac{\beta}{g_m} = \frac{100}{92} \text{ k}\Omega = 1.09 \text{ k}\Omega$$

$$r_e = \frac{V_T}{I_E} = \frac{25 \text{ mV}}{(2.3 / 0.99) \text{ mA}} = 10.8 \Omega$$

BJT Small Signal

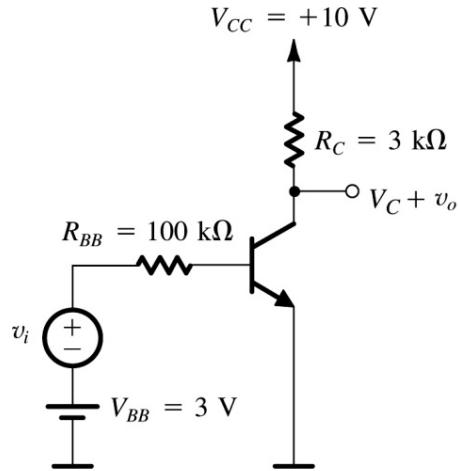


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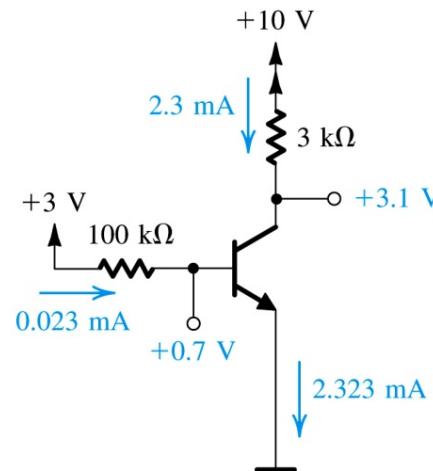
EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

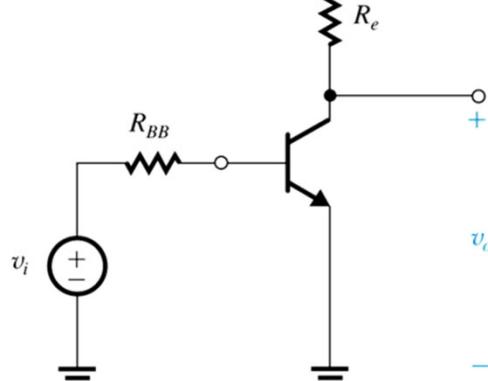
See Sedra example
6.14 for more details



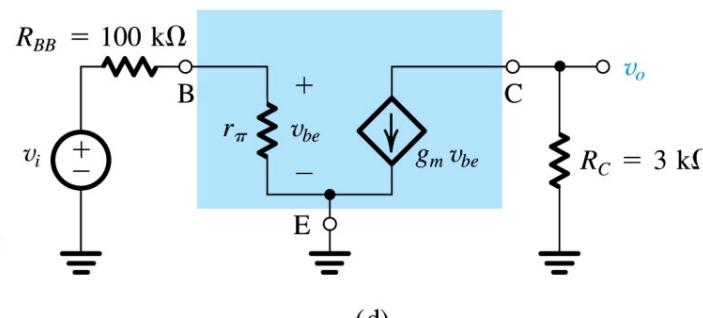
(a)



(b)



(c)



(d)

$$g_m = \frac{I_C}{V_T} = \frac{2.3 \text{ mA}}{25 \text{ mV}} = 92 \text{ mA/V}$$

$$r_\pi = \frac{\beta}{g_m} = \frac{100}{92} \text{ k}\Omega = 1.09 \text{ k}\Omega$$

$$r_e = \frac{V_T}{I_E} = \frac{25 \text{ mV}}{(2.3 / 0.99) \text{ mA}} = 10.8 \Omega$$

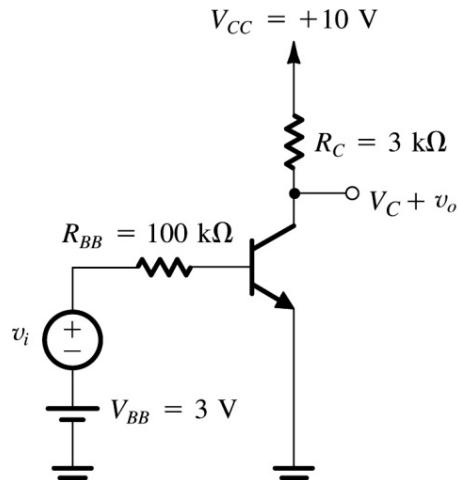
BJT Small Signal



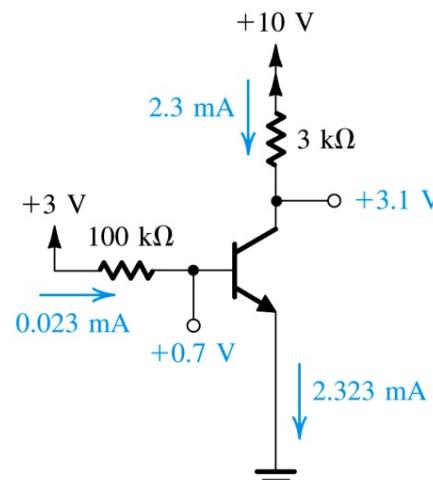
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EXAMPLE

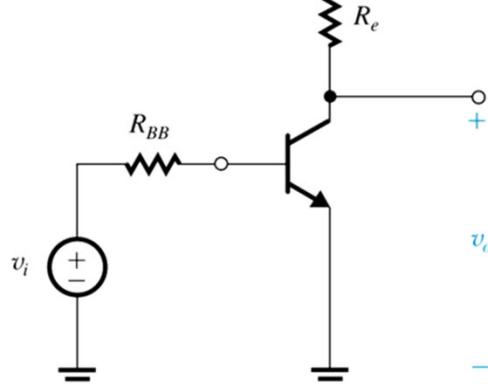
Find the voltage gain of the following amplifier ($\beta=100$)



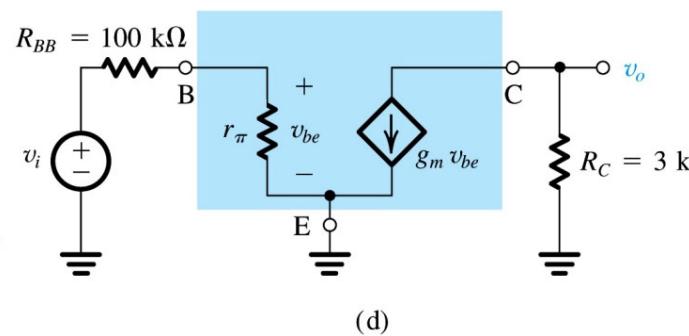
(a)



(b)



(c)



(d)

See Sedra example
6.14 for more details

$$g_m = \frac{I_C}{V_T} = \frac{2.3 \text{ mA}}{25 \text{ mV}} = 92 \text{ mA/V}$$

$$r_\pi = \frac{\beta}{g_m} = \frac{100}{92} \text{ k}\Omega = 1.09 \text{ k}\Omega$$

$$r_e = \frac{V_T}{I_E} = \frac{25 \text{ mV}}{(2.3 / 0.99) \text{ mA}} = 10.8 \Omega$$

$$v_{be} = v_i \frac{r_\pi}{R_{BB} + r_\pi} = 0.011 v_i$$

$$v_o = -R_C g_m v_{be} = -3.04 v_i$$

$$A_v = \frac{v_o}{v_i} = -3.04$$

BJT Small Signal

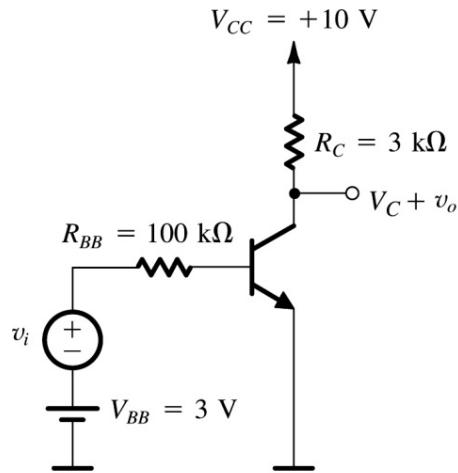


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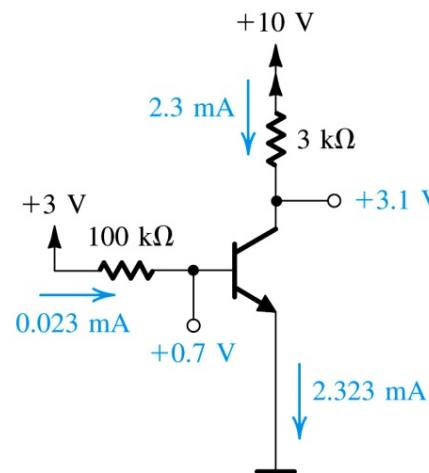
EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

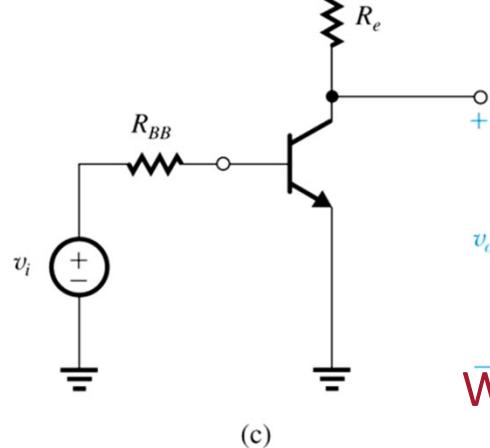
See Sedra example
6.14 for more details



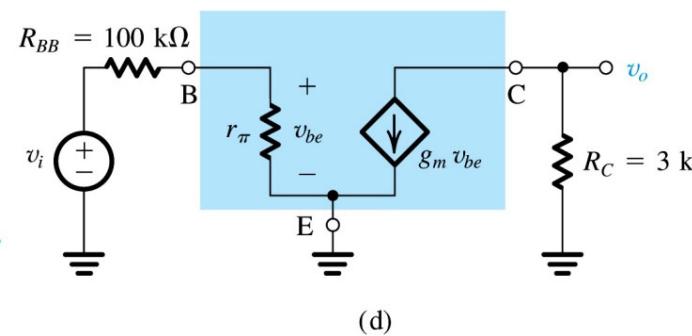
(a)



(b)



(c)



(d)

$$g_m = \frac{I_C}{V_T} = \frac{2.3 \text{ mA}}{25 \text{ mV}} = 92 \text{ mA/V}$$

$$r_\pi = \frac{\beta}{g_m} = \frac{100}{92} \text{ k}\Omega = 1.09 \text{ k}\Omega$$

$$r_e = \frac{V_T}{I_E} = \frac{25 \text{ mV}}{(2.3 / 0.99) \text{ mA}} = 10.8 \Omega$$

$$v_{be} = v_i \frac{r_\pi}{R_{BB} + r_\pi} = 0.011 v_i$$

$$v_o = -R_C g_m v_{be} = -3.04 v_i$$

$$A_v = \frac{v_o}{v_i} = -3.04$$

We must make sure the BJT *remains* in active mode!

BJT Small Signal

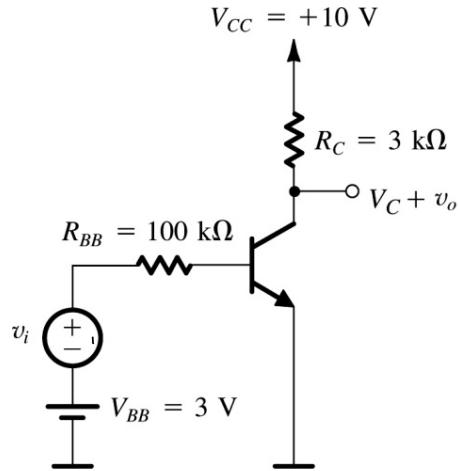
EXAMPLE



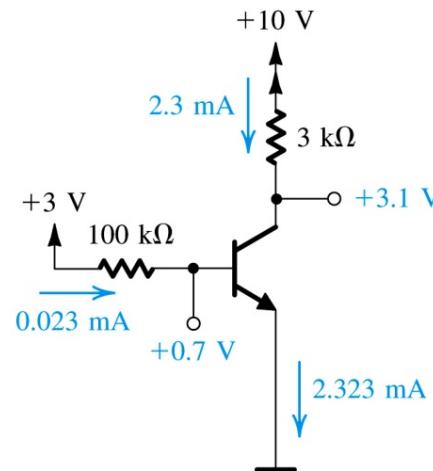
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Find the voltage gain of the following amplifier ($\beta=100$)

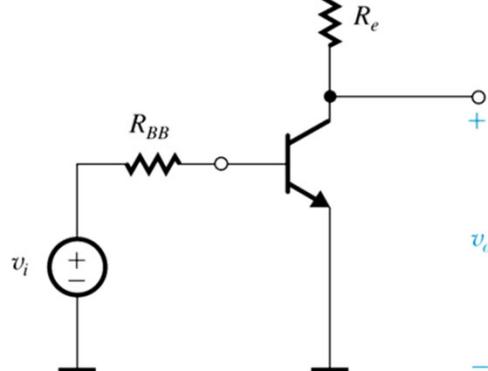
See Sedra example
6.14 for more details



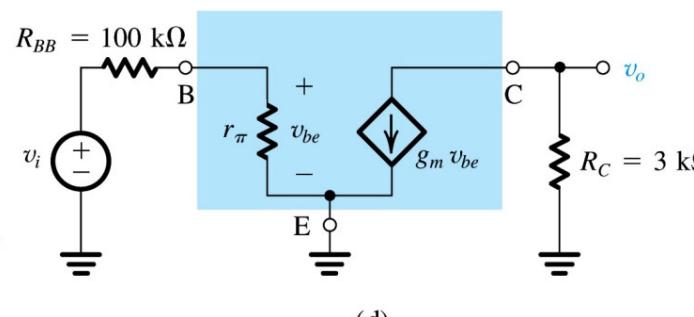
(a)



(b)



(c)



(d)

$$v_{be} = v_i \frac{r_\pi}{R_{BB} + r_\pi} = 0.011v_i$$

$$v_o = -R_C g_m v_{be} = -3.04v_i$$

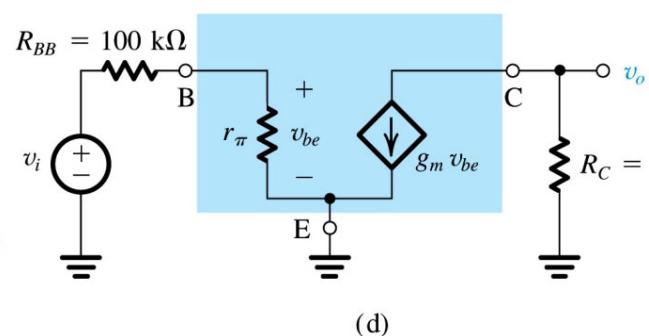
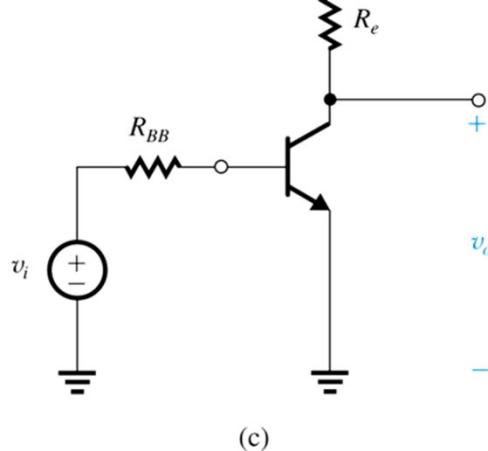
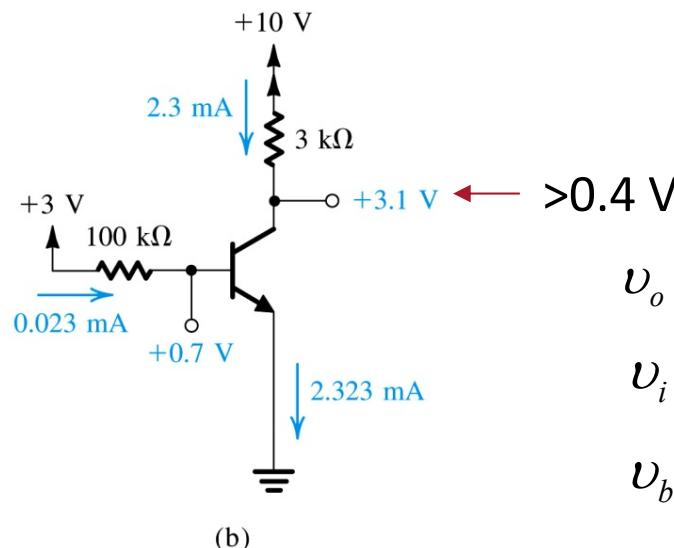
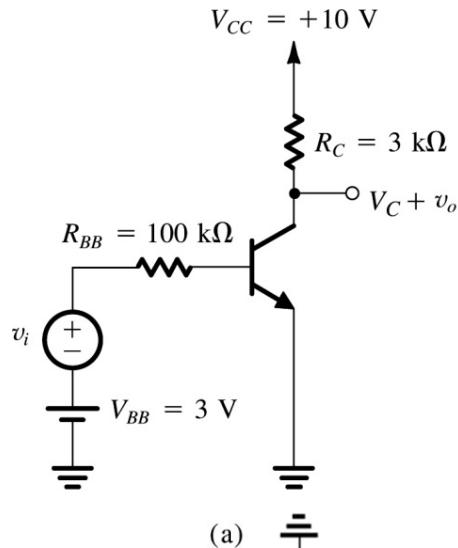
$$A_v = \frac{v_o}{v_i} = -3.04$$

BJT Small Signal

EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
6.15 for more details



$$v_o = 2.7 \text{ V} \text{ (swing)}$$

$$v_i = v_o / \text{gain} = 0.88 \text{ V}$$

$$v_{be} = 0.011v_i = 9.6 \text{ mV}$$

$$v_{be} = v_i \frac{r_\pi}{R_{BB} + r_\pi} = 0.011v_i$$

$$v_o = -R_C g_m v_{be} = -3.04v_i$$

$$A_v = \frac{v_o}{v_i} = -3.04$$

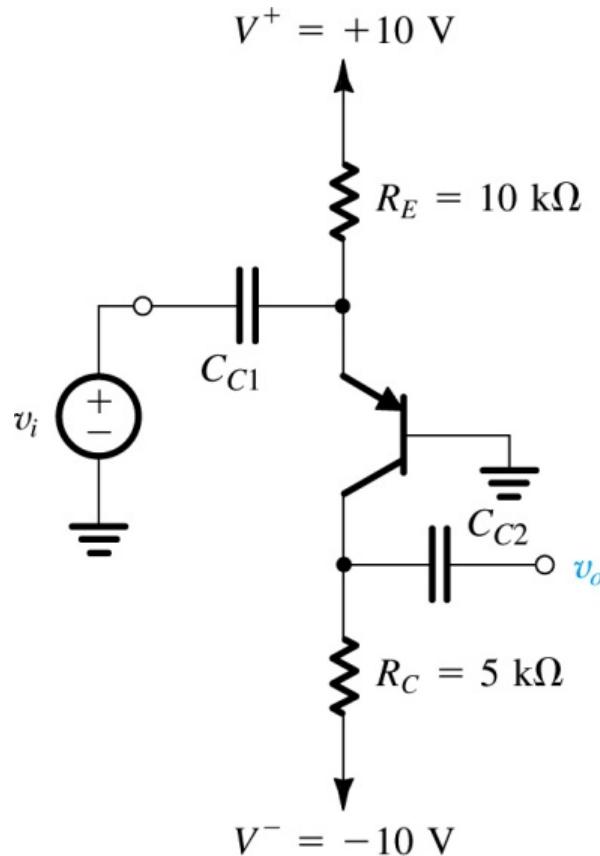
BJT Small Signal



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EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)



(a)

What type of amplifier configuration is this?



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Common Emitter

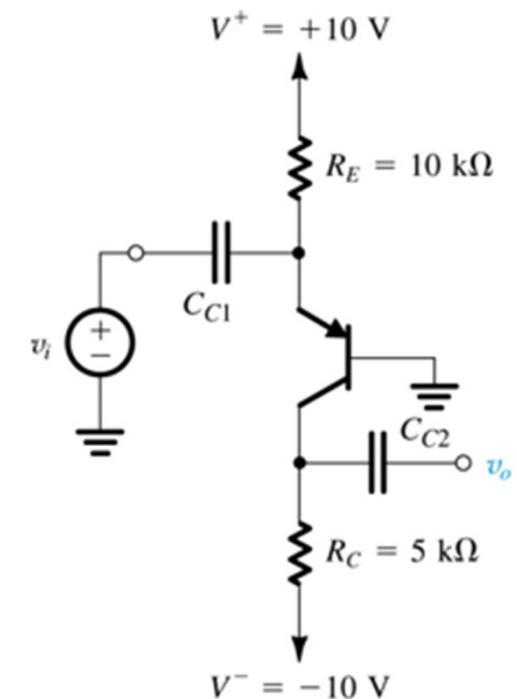
Common Base

Common Collector

0%

0%

0%

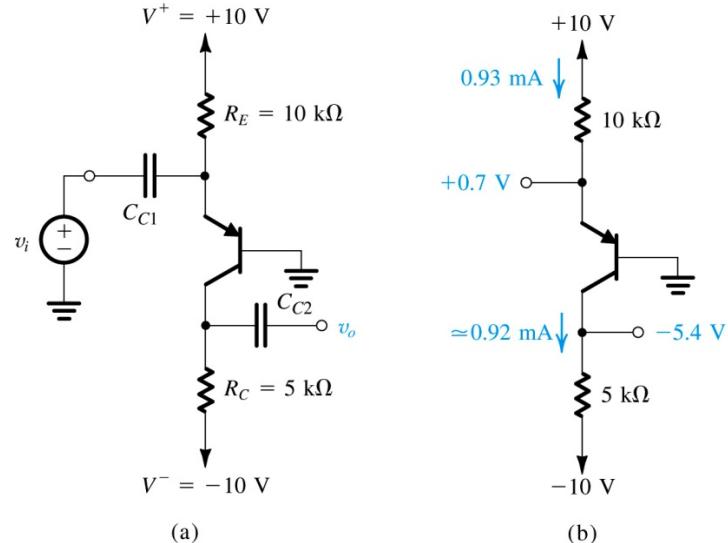


BJT Small Signal

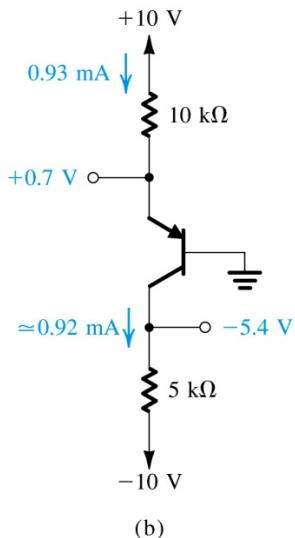
EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
6.16 for more details



(a)



(b)

BJT Small Signal

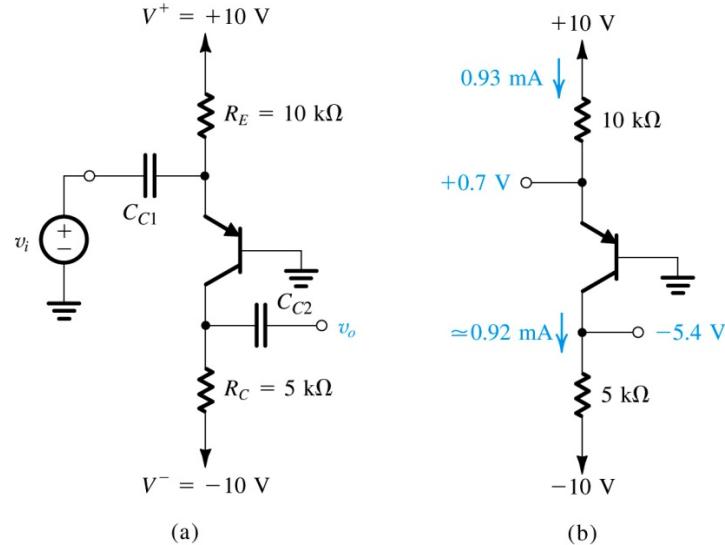


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EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
6.16 for more details



$$g_m = \frac{I_C}{V_T} = \frac{0.92 \text{ mA}}{0.025 \text{ V}} = 36.8 \text{ mA/V}$$

$$r_e = \frac{V_T}{I_E} = \frac{0.025 \text{ V}}{0.92 \text{ mA}} = 27.2 \Omega$$

$$\beta = 100 \quad \alpha = 0.99$$

BJT Small Signal

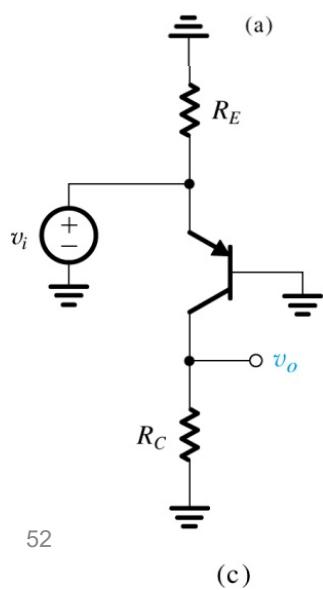
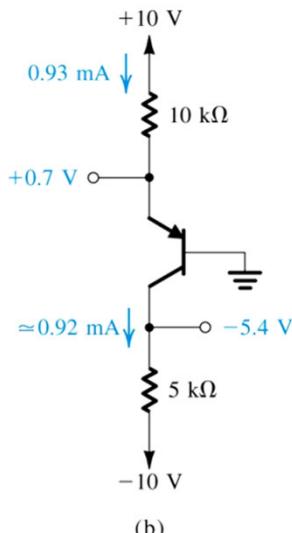
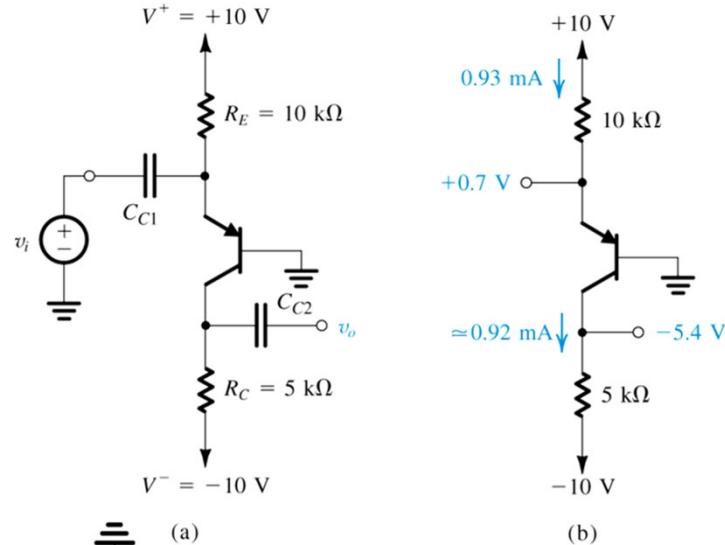


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EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
6.16 for more details



$$g_m = \frac{I_C}{V_T} = \frac{0.92\text{ mA}}{0.025\text{ V}} = 36.8\text{ mA/V}$$

$$r_e = \frac{V_T}{I_E} = \frac{0.025\text{ V}}{0.92\text{ mA}} = 27.2\text{ }\Omega$$

$$\beta = 100 \quad \alpha = 0.99$$

BJT Small Signal

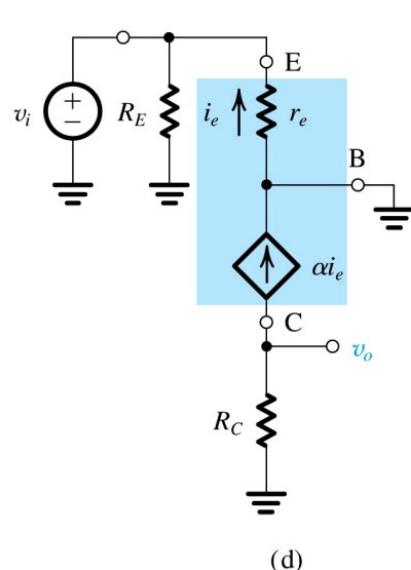
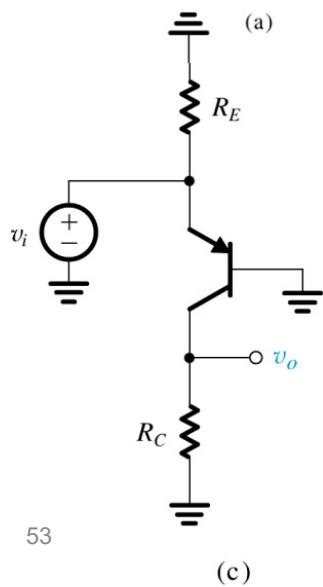
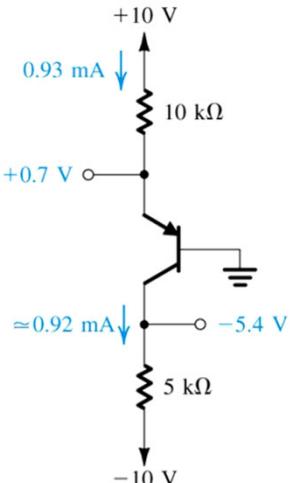
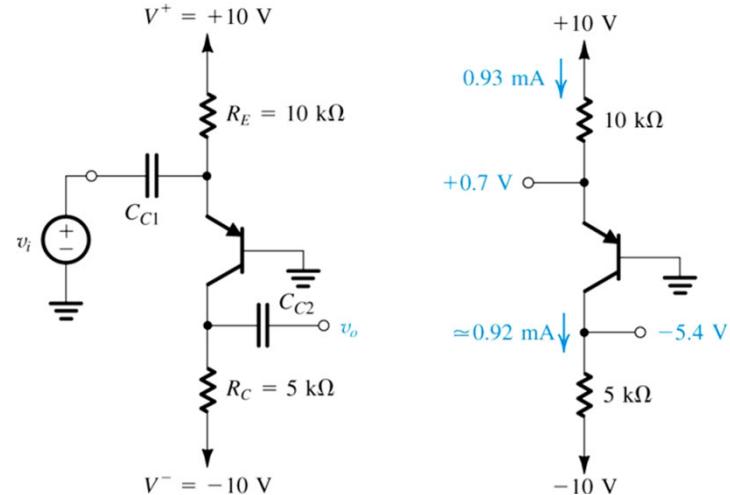


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EXAMPLE

Find the voltage gain of the following amplifier ($\beta=100$)

See Sedra example
4.16 for more details



$$g_m = \frac{I_C}{V_T} = \frac{0.92\text{ mA}}{0.025\text{ V}} = 36.8 \text{ mA/V}$$

$$r_e = \frac{V_T}{I_E} = \frac{0.025\text{ V}}{0.92\text{ mA}} = 27.2 \Omega$$

$$\beta = 100 \quad \alpha = 0.99$$

$$i_e = -\frac{v_i}{r_e}$$

$$v_o = -\alpha i_e R_C$$

$$= \frac{\alpha R_C}{r_e} v_i$$

$$v_o = -\alpha i_e R_C = \alpha R_C \frac{v_i}{r_e}$$

$$A_v = \frac{v_o}{v_i} = 182$$

BJT Small Signal



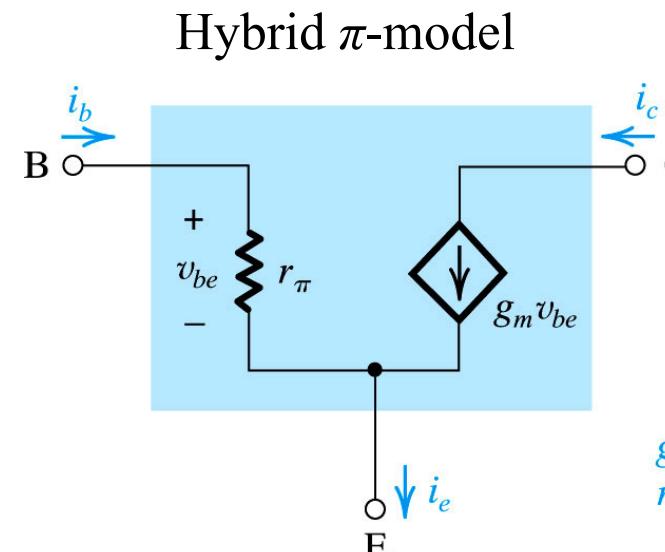
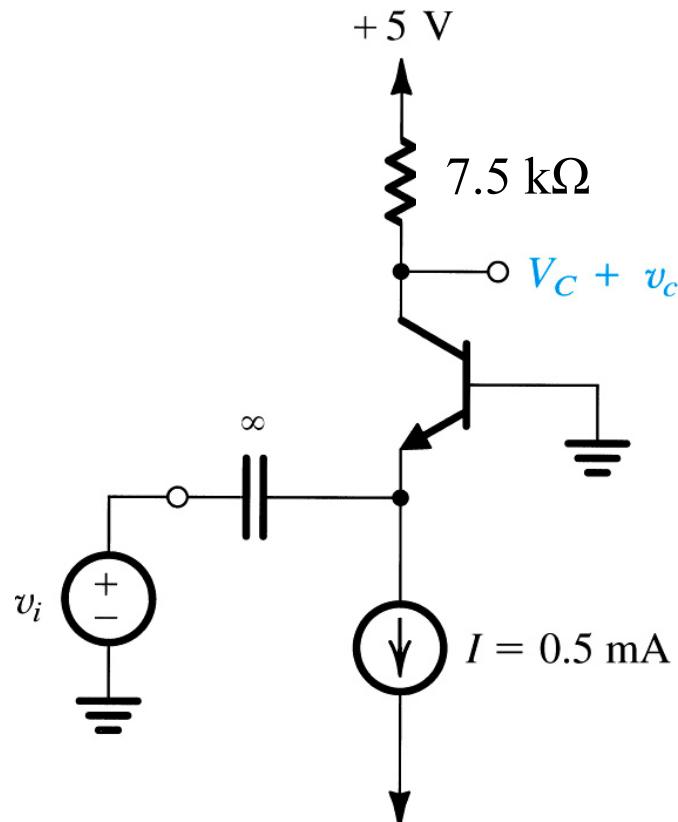
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BIASING WITH A CURRENT SOURCE

The transistor amplifier below is biased with a current source and has a very high β .

Find the dc voltage at the collector, V_C . Find the value of g_m .

Replace the transistor with the simplifier hybrid π -model shown and use it to find the voltage gain.



$$g_m = I_C / V_T$$

$$r_\pi = \beta / g_m$$

(a)

This week

TUTORIAL + FIRST ASSIGNMENT

Tutorial Workshop:

- The worksheet is available on iLearn
- There are several practice questions on Diodes and BJTs
- Try your best to solve them all before the workshop session, if you need help, come along to the workshop and speak to the tutors
- Tutorial workshops are not graded, this is just for practice. It will help you a lot with the assignment and exam!

First Assignment!

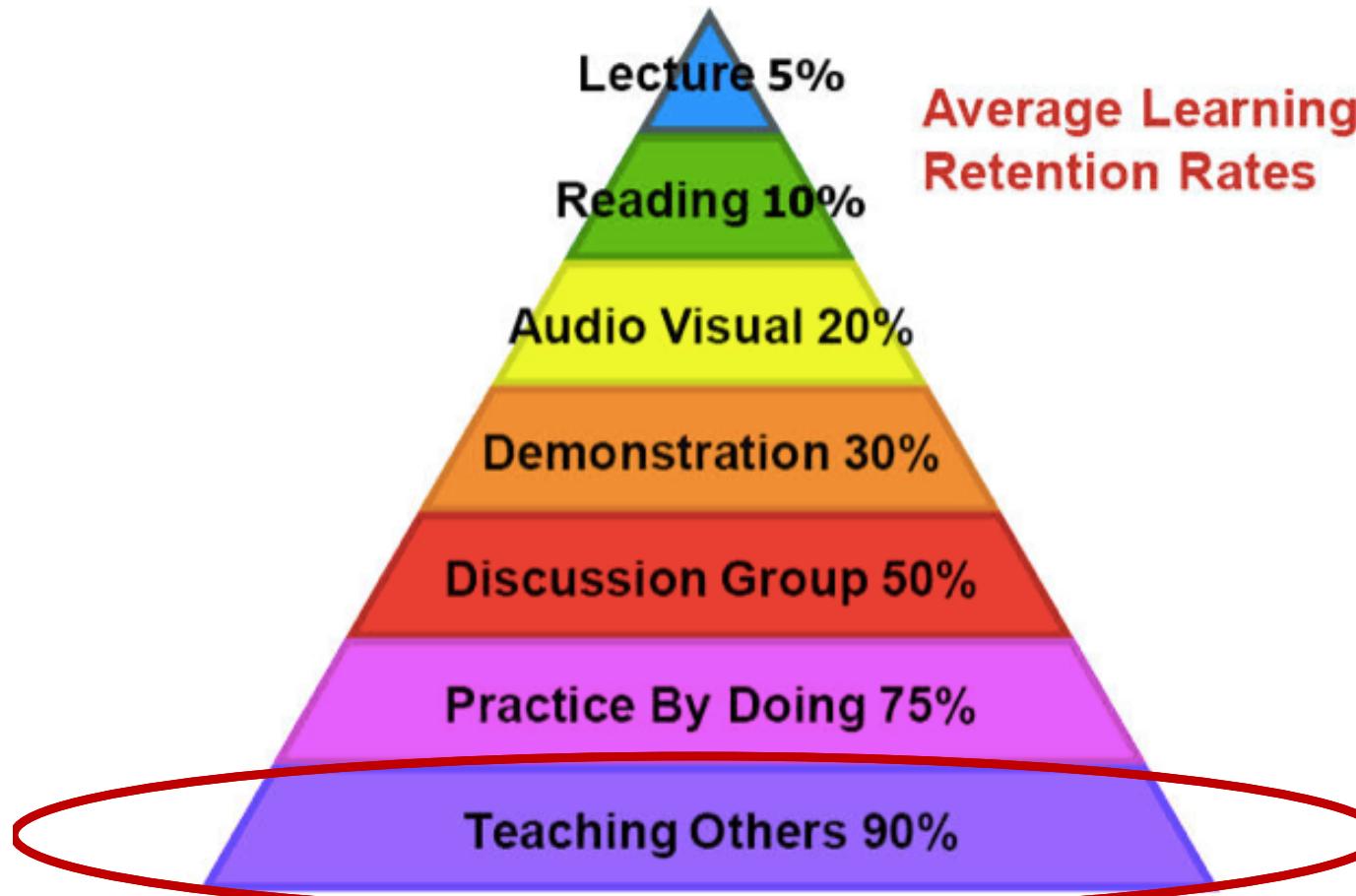
- The first assignment is available now.
- An iLearn quiz on the topics of diodes and BJTs
- Final question requires video Submission!
- Submission is due by 11:55pm Friday 25th August

Assignment



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WHY A VIDEO EXPLAINER?



- Teaching a topic helps you to retain the learning!
- This also gives you a chance to work on your communication skills

Source: National Training Laboratories, Bethel, Maine